



June 2007

LME49860

44V Dual High Performance, High Fidelity Audio Operational Amplifier

General Description

The LME49860 is part of the ultra-low distortion, low noise, high slew rate operational amplifier series optimized and fully specified for high performance, high fidelity applications. Combining advanced leading-edge process technology with state-of-the-art circuit design, the LME49860 audio operational amplifiers deliver superior audio signal amplification for outstanding audio performance. The LME49860 combines extremely low voltage noise density ($2.7\text{nV}/\sqrt{\text{Hz}}$) with vanishingly low THD+N (0.00003%) to easily satisfy the most demanding audio applications. To ensure that the most challenging loads are driven without compromise, the LME49860 has a high slew rate of $\pm 20\text{V}/\mu\text{s}$ and an output current capability of $\pm 26\text{mA}$. Further, dynamic range is maximized by an output stage that drives $2\text{k}\Omega$ loads to within 1V of either power supply voltage and to within 1.4V when driving 600Ω loads.

The LME49860's outstanding CMRR (120dB), PSRR (120dB), and V_{OS} (0.1mV) give the amplifier excellent operational amplifier DC performance.

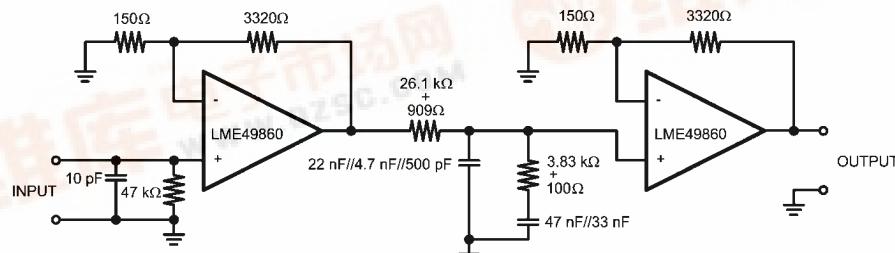
The LME49860 has a wide supply range of $\pm 2.5\text{V}$ to $\pm 22\text{V}$. Over this supply range the LME49860 maintains excellent common-mode rejection, power supply rejection, and low input bias current. The LME49860 is unity gain stable. This Audio Operational Amplifier achieves outstanding AC performance while driving complex loads with values as high as 100pF.

The LME49860 is available in 8-lead narrow body SOIC and 8-lead Plastic DIP packages. Demonstration boards are available for each package.

Key Specifications

- Power Supply Voltage Range $\pm 2.5\text{V}$ to $\pm 22\text{V}$
- THD+N
($A_V = 1$, $V_{OUT} = 3\text{V}_{RMS}$, $f_{IN} = 1\text{kHz}$)

Typical Application



Note: 1% metal film resistors, 5% polypropylene capacitors

Passively Equalized RIAA Phono Preamplifier

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LME49860 44V Dual High Performance, High Fidelity Audio Operational Amplifier

$R_L = 2\text{k}\Omega$	0.00003% (typ)
$R_L = 600\Omega$	0.00003% (typ)
■ Input Noise Density	$2.7\text{nV}/\sqrt{\text{Hz}}$ (typ)
■ Slew Rate	$\pm 20\text{V}/\mu\text{s}$ (typ)
■ Gain Bandwidth Product	55MHz (typ)
■ Open Loop Gain ($R_L = 600\Omega$)	140dB (typ)
■ Input Bias Current	10nA (typ)
■ Input Offset Voltage	0.1mV (typ)
■ DC Gain Linearity Error	0.000009%

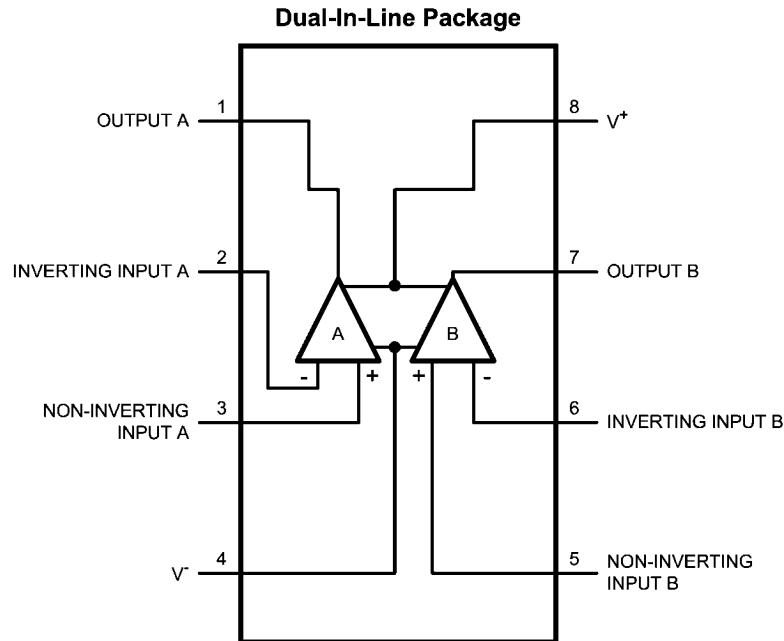
Features

- Easily drives 600Ω loads
- Optimized for superior audio signal fidelity
- Output short circuit protection
- PSRR and CMRR exceed 120dB (typ)
- SOIC, DIP packages

Applications

- Ultra high quality audio amplification
- High fidelity preamplifiers
- High fidelity multimedia
- State of the art phono pre amps
- High performance professional audio
- High fidelity equalization and crossover networks
- High performance line drivers
- High performance line receivers
- High fidelity active filters

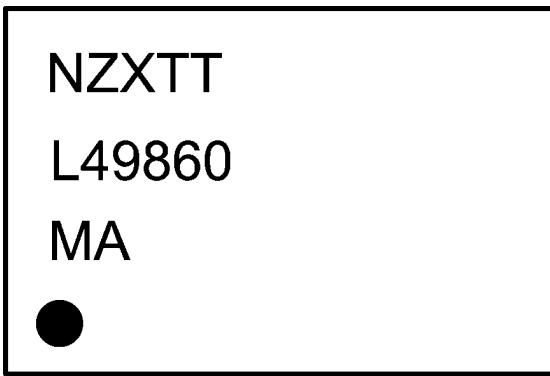
Connection Diagrams



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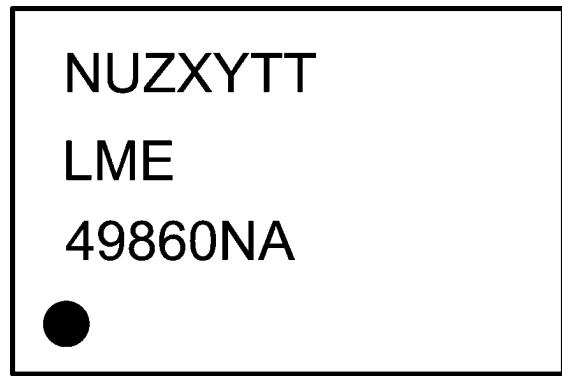
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See NS Package Number — M08A
Order Number LME49860NA
See NS Package Number — N08E

LME49860MA Top Mark



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N — National Logo
Z — Assembly Plant code
X — 1 Digit Date code
TT — Die Traceability
L49860 — LME49860
MA — Package code

LME49860NA Top Mark



20215102
N — National Logo
U — Fabrication code
Z — Assembly Plant code
XY — 2 Digit Date code
TT — Die Traceability
NA — Package code

Absolute Maximum Ratings (Notes 1, 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Power Supply Voltage ($V_S = V^+ - V^-$)	46V
Storage Temperature	-65°C to 150°C
Input Voltage ($V^- - 0.7V$ to $(V^+) + 0.7V$)	
Output Short Circuit (Note 3)	Continuous
ESD Susceptibility (Note 4)	2000V
ESD Susceptibility (Note 5)	
Pins 1, 4, 7 and 8	200V

Pins 2, 3, 5 and 6	100V
Junction Temperature	150°C
Thermal Resistance	
θ_{JA} (SO)	145°C/W
θ_{JA} (NA)	102°C/W

Operating Ratings

Temperature Range	
$T_{MIN} \leq T_A \leq T_{MAX}$	-40°C ≤ T_A ≤ 85°C
Supply Voltage Range	$\pm 2.5V \leq V_S \leq \pm 22V$

Electrical Characteristics for the LME49860 (Note 1) The following specifications apply for $V_S = \pm 18V$ and $\pm 22V$, $R_L = 2k\Omega$, $R_{SOURCE} = 10\Omega$, $f_{IN} = 1kHz$, $T_A = 25^\circ C$, unless otherwise specified.

Symbol	Parameter	Conditions	LME49860		Units (Limits)
			Typical	Limit	
			(Note 6)	(Note 7)	
THD+N	Total Harmonic Distortion + Noise	$A_V = 1$, $V_{OUT} = 3V_{rms}$ $R_L = 2k\Omega$ $R_L = 600\Omega$	0.00003	0.00009	% (max)
IMD	Intermodulation Distortion	$A_V = 1$, $V_{OUT} = 3V_{RMS}$ Two-tone, 60Hz & 7kHz 4:1	0.00005		%
GBWP	Gain Bandwidth Product		55	45	MHz (min)
SR	Slew Rate		±20	±15	V/μs (min)
FPBW	Full Power Bandwidth	$V_{OUT} = 1V_{P-P}$, -3dB referenced to output magnitude at $f = 1kHz$	10		MHz
t_s	Settling time	$A_V = -1$, 10V step, $C_L = 100pF$ 0.1% error range	1.2		μs
e_n	Equivalent Input Noise Voltage	$f_{BW} = 20Hz$ to $20kHz$	0.34	0.65	μV _{RMS} (max)
	Equivalent Input Noise Density	$f = 1kHz$ $f = 10Hz$	2.7 6.4	4.7	nV/√Hz (max)
i_n	Current Noise Density	$f = 1kHz$ $f = 10Hz$	1.6 3.1		pA/√Hz
V_{OS}	Offset Voltage	$V_S = \pm 18V$	±0.12	±0.7	mV (max)
		$V_S = \pm 22V$	±0.14	±0.7	mV (max)
$\Delta V_{OS}/\Delta Temp$	Average Input Offset Voltage Drift vs Temperature	-40°C ≤ T_A ≤ 85°C	0.2		μV/°C
PSRR	Average Input Offset Voltage Shift vs Power Supply Voltage	(Note 8) $V_S = \pm 18V$, $\Delta V_S = 24V$ $V_S = \pm 22V$, $\Delta V_S = 30V$	120		dB
			120	110	dB (min)
ISO _{CH-CH}	Channel-to-Channel Isolation	$f_{IN} = 1kHz$ $f_{IN} = 20kHz$	118 112		dB
I_B	Input Bias Current	$V_{CM} = 0V$	10	72	nA (max)
$\Delta I_{OS}/\Delta Temp$	Input Bias Current Drift vs Temperature	-40°C ≤ T_A ≤ 85°C	0.1		nA/°C
I_{OS}	Input Offset Current	$V_{CM} = 0V$	11	65	nA (max)
V_{IN-CM}	Common-Mode Input Voltage Range	$V_S = \pm 18V$	+17.1 -16.9	(V+) - 2.0 (V-) + 2.0	V (min) V (min)
		$V_S = \pm 22V$	+21.0 -20.8	(V+) - 2.0 (V-) + 2.0	V (min) V (min)



Symbol	Parameter	Conditions	LME49860		Units (Limits)
			Typical	Limit	
			(Note 6)	(Note 7)	
CMRR	Common-Mode Rejection	$V_S = \pm 18V$ $-12V \leq V_{CM} \leq 12V$	120		dB
		$V_S = \pm 22V$ $-15V \leq V_{CM} \leq 15V$	120	110	
Z_{IN}	Differential Input Impedance		30		kΩ
	Common Mode Input Impedance	$-10V < V_{cm} < 10V$	1000		MΩ
A_{VOL}	Open Loop Voltage Gain	$V_S = \pm 18V$ $-12V \leq V_{out} \leq 12V$ $R_L = 600\Omega$ $R_L = 2k\Omega$ $R_L = 10k\Omega$	140		dB
		$V_S = \pm 22V$ $-15V \leq V_{out} \leq 15V$ $R_L = 600\Omega$ $R_L = 2k\Omega$ $R_L = 10k\Omega$	140	125	
		$R_L = 600\Omega$ $R_L = 2k\Omega$ $R_L = 10k\Omega$	140		
		$V_S = \pm 18V$ $V_S = \pm 22V$	± 16.7	± 19.0	V
		$R_L = 2k\Omega$ $V_S = \pm 18V$ $V_S = \pm 22V$	± 17.0		V
		$R_L = 10k\Omega$ $V_S = \pm 18V$ $V_S = \pm 22V$	± 17.1		V
I_{OUT}	Output Current	$R_L = 600\Omega$ $V_S = \pm 20V$ $V_S = \pm 22V$	± 31	± 30	mA
I_{OUT-cc}	Instantaneous Short Circuit Current		$+53$ -42		mA
R_{OUT}	Output Impedance	$f_{IN} = 10kHz$ Closed-Loop Open-Loop	0.01 13		Ω
C_{LOAD}	Capacitive Load Drive Overshoot	100pF	16		%
I_S	Total Quiescent Current	$I_{OUT} = 0mA$ $V_S = \pm 18V$ $V_S = \pm 22V$	10.2 10.5	13	mA mA (max)

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur.

Note 2: Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

Note 3: Amplifier output connected to GND, any number of amplifiers within a package.

Note 4: Human body model, 100pF discharged through a 1.5kΩ resistor.

Note 5: Machine Model ESD test is covered by specification EIAJ IC-121-1981. A 200pF cap is charged to the specified voltage and then discharged directly into the IC with no external series resistor (resistance of discharge path must be under 50Ω).

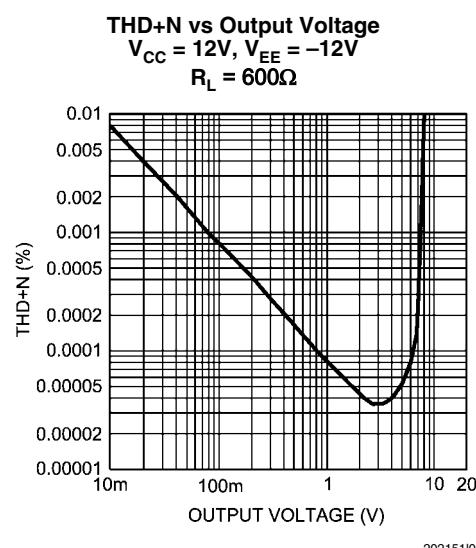
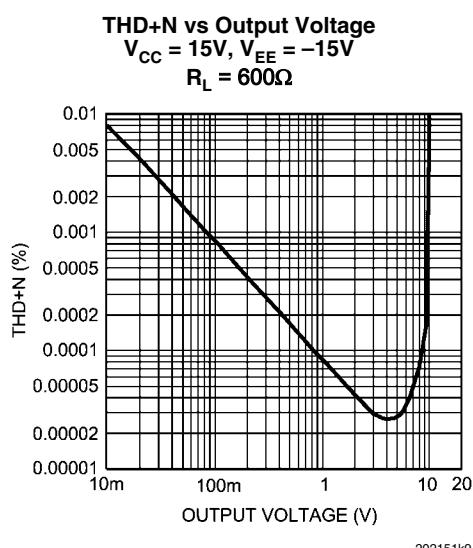
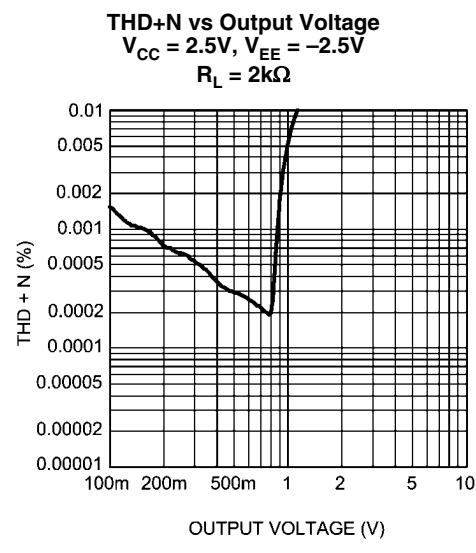
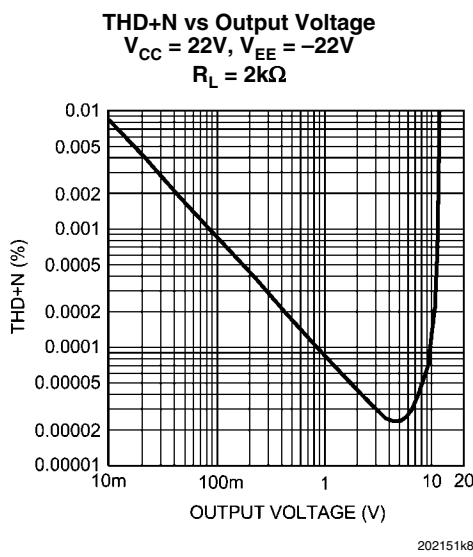
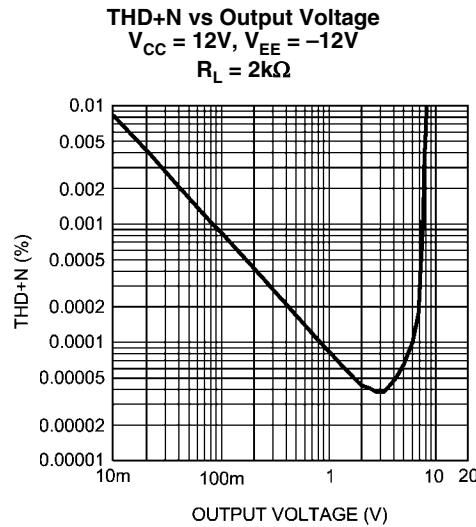
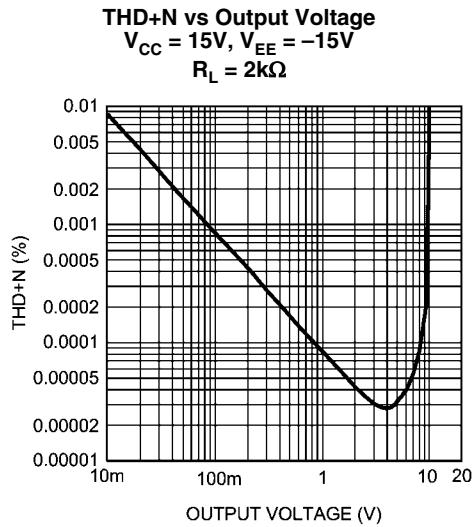
Note 6: Typical specifications are specified at +25°C and represent the most likely parametric norm.

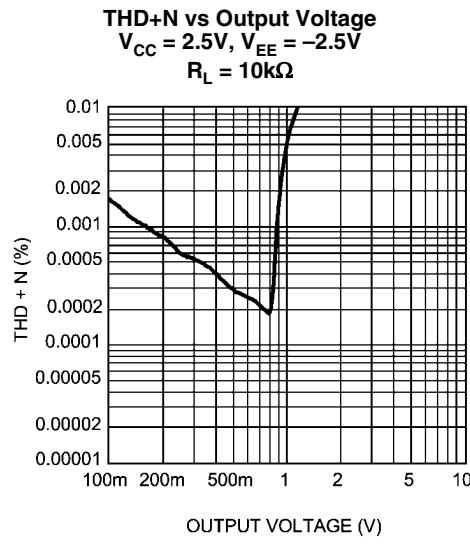
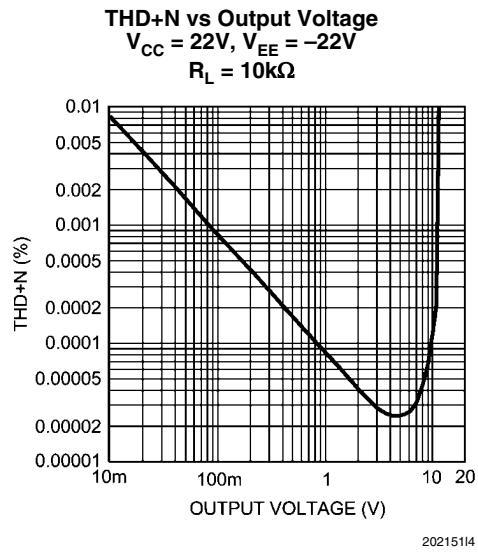
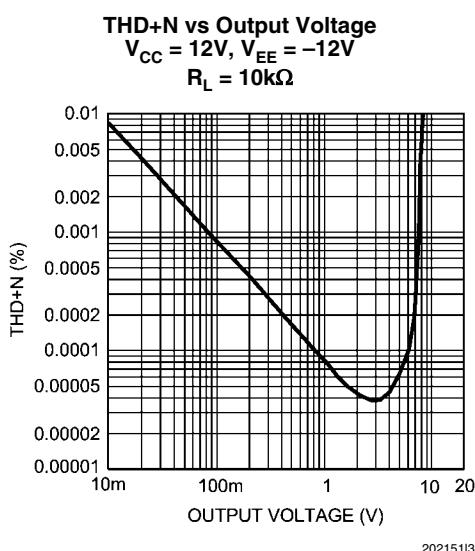
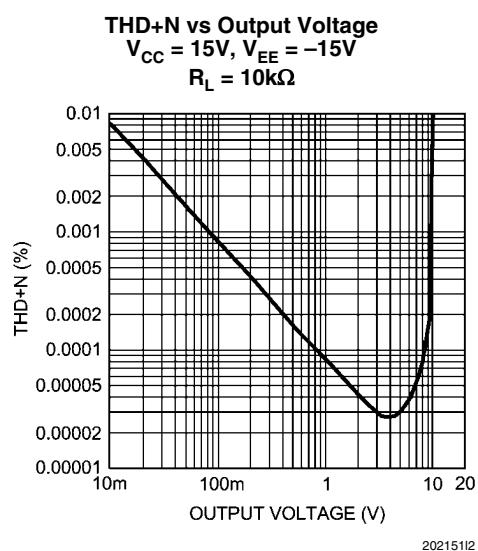
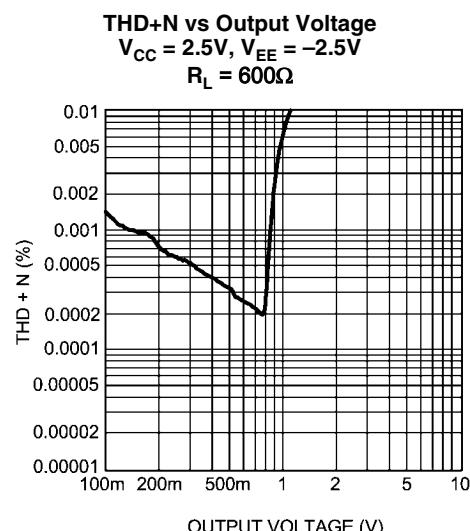
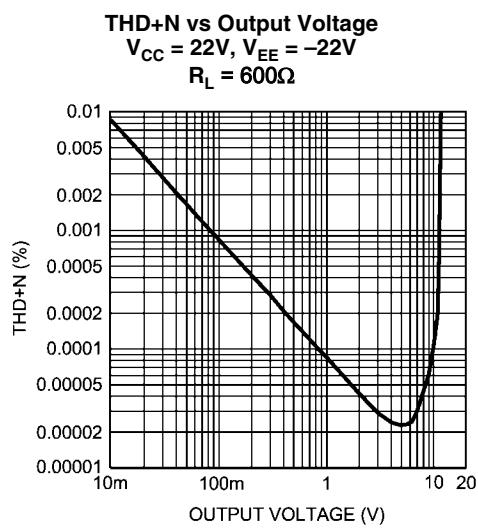
Note 7: Tested limits are guaranteed to National's AOQL (Average Outgoing Quality Level).

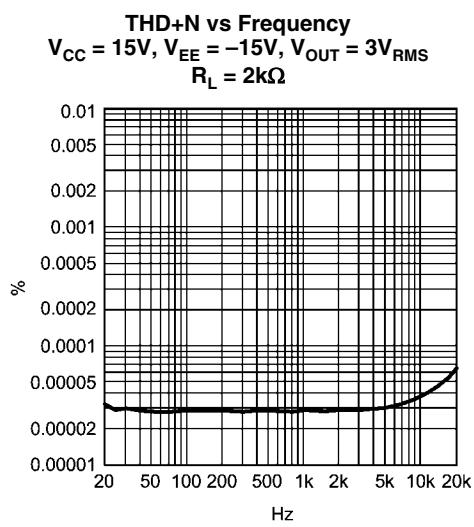
Note 8: PSRR is measured as follows: For $V_S = \pm 22V$, V_{OS} is measured at two supply voltages, ±7V and ±22V. $PSRR = 20\log(\Delta V_{OS}/\Delta V_S) I$.



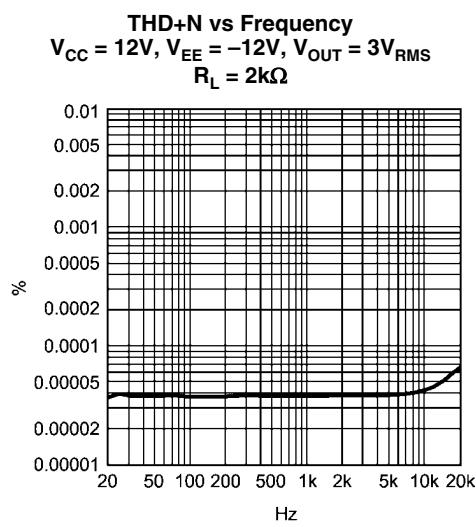
Typical Performance Characteristics



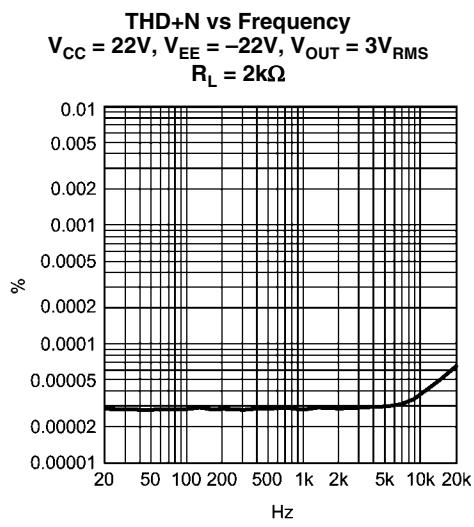




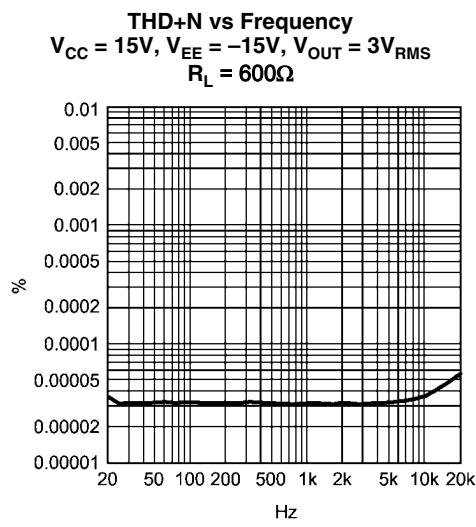
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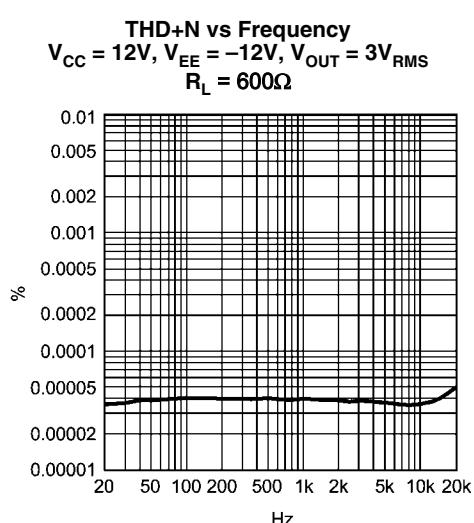
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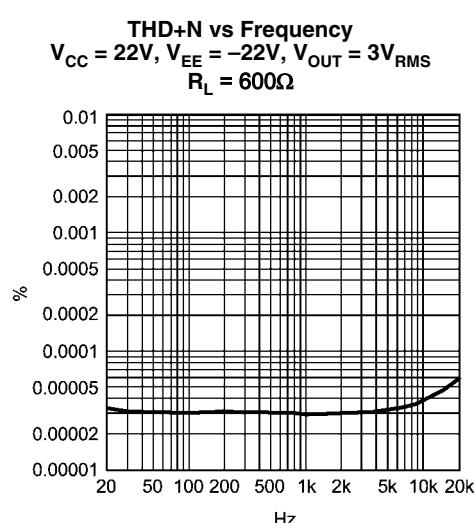
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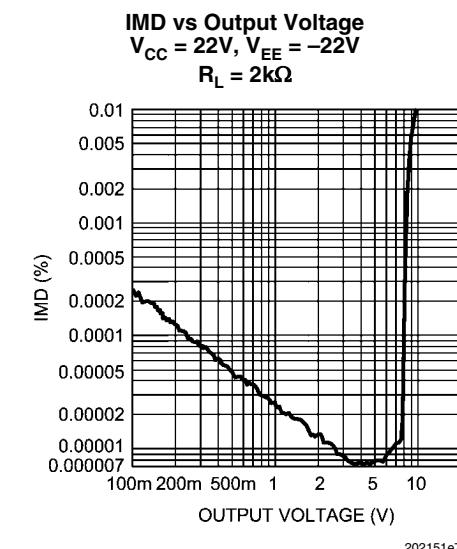
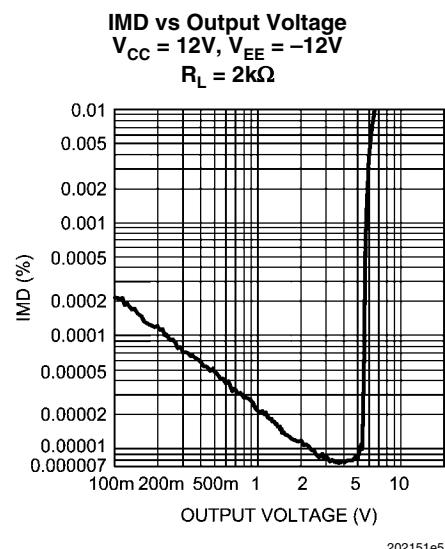
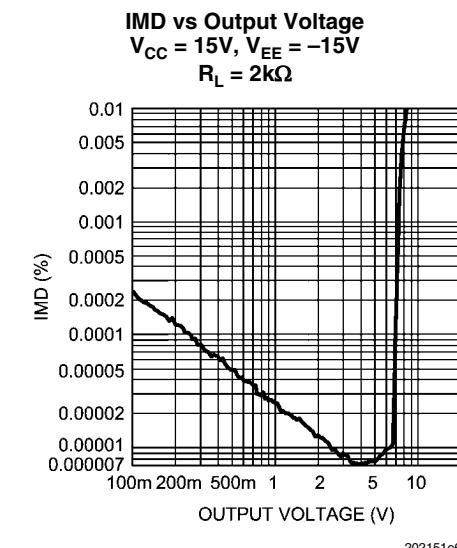
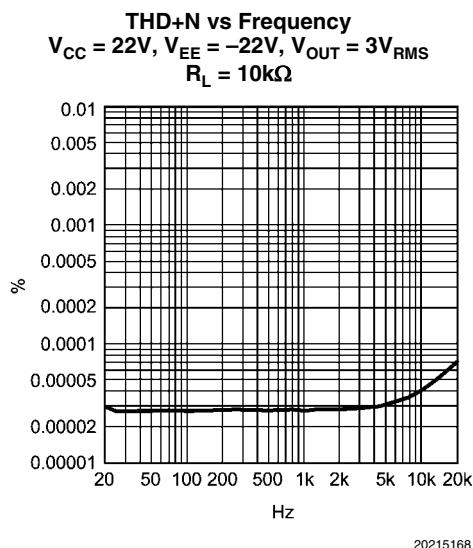
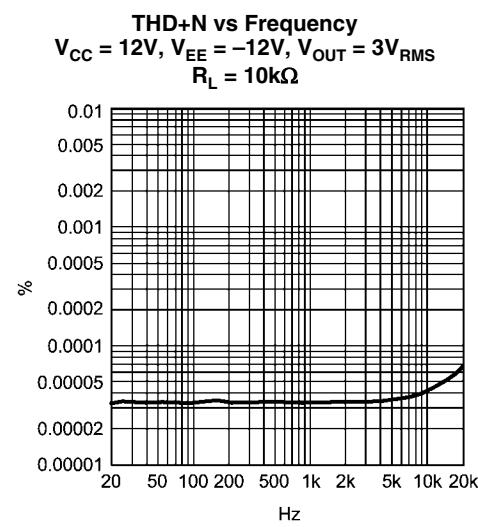
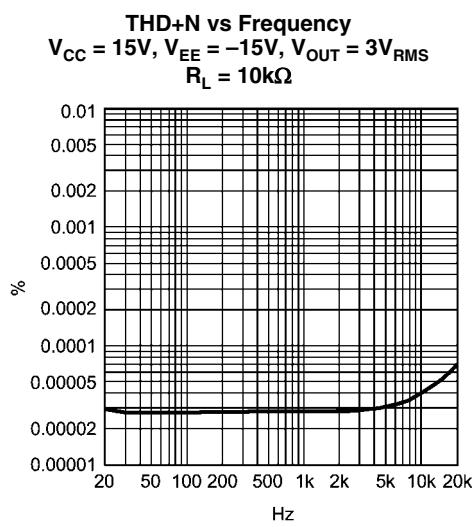
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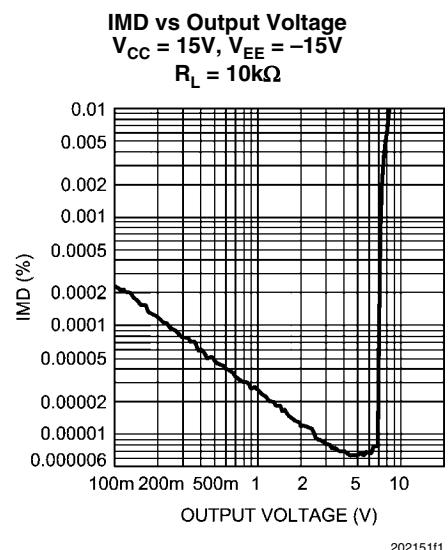
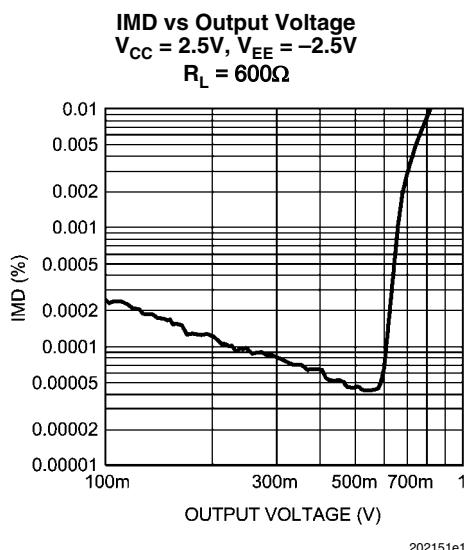
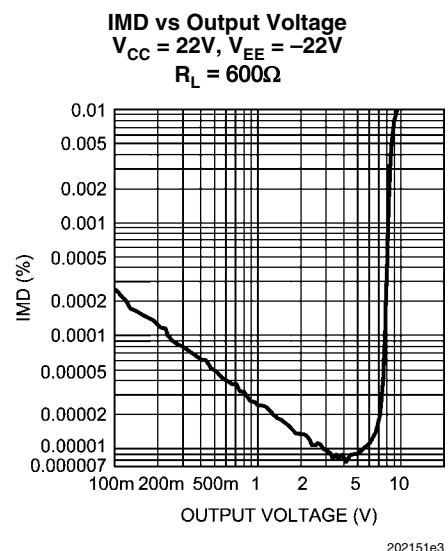
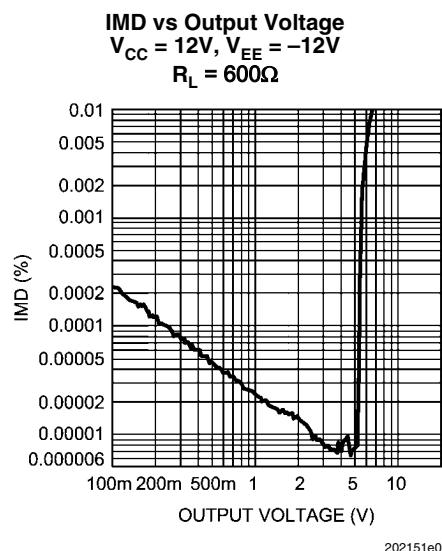
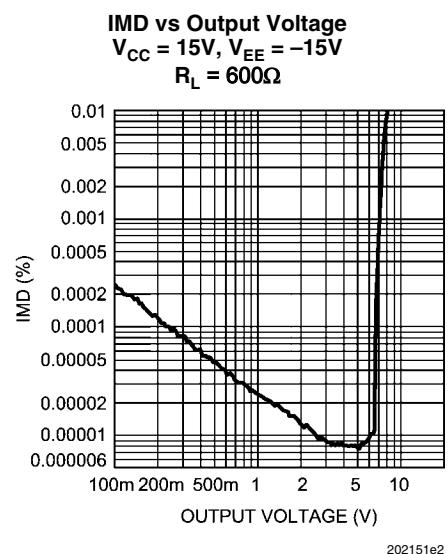
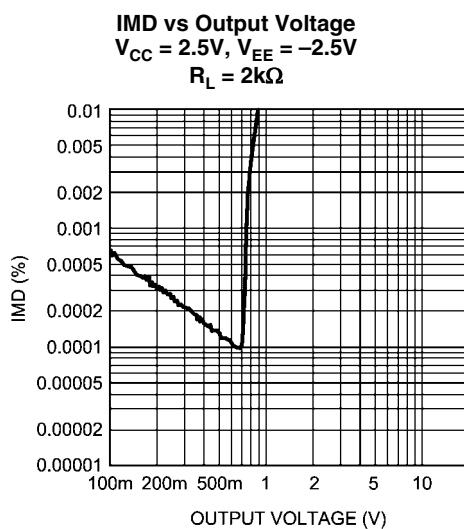


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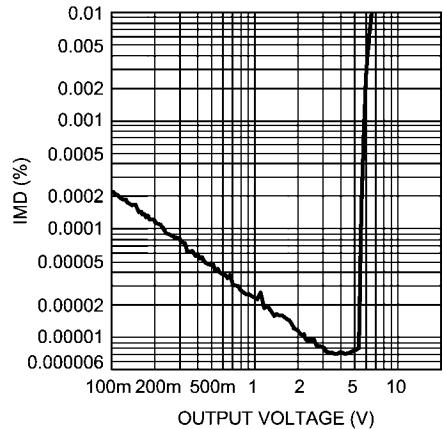


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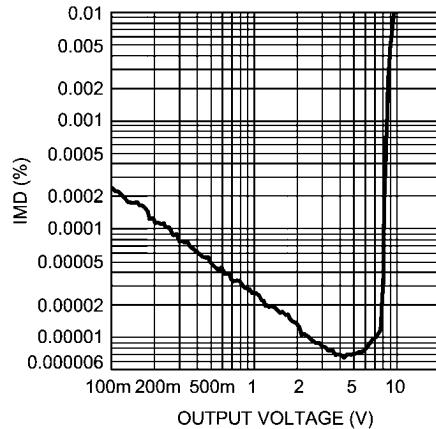




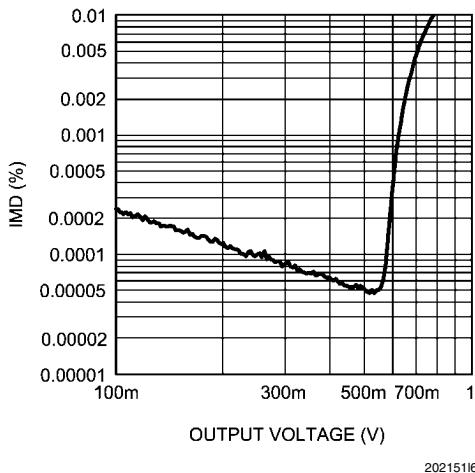
IMD vs Output Voltage
 $V_{CC} = 12V$, $V_{EE} = -12V$
 $R_L = 10k\Omega$



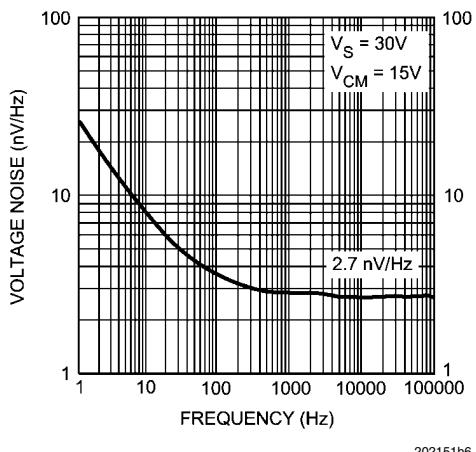
IMD vs Output Voltage
 $V_{CC} = 22V$, $V_{EE} = -22V$
 $R_L = 10k\Omega$



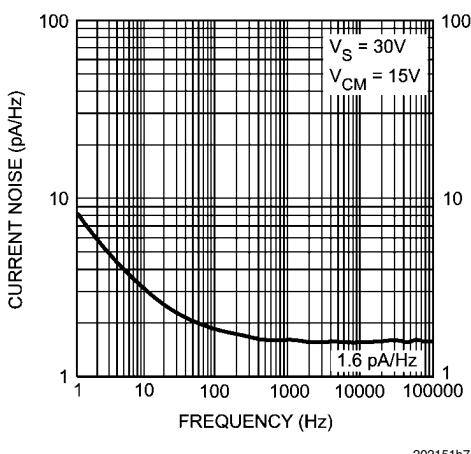
IMD vs Output Voltage
 $V_{CC} = 2.5V$, $V_{EE} = -2.5V$
 $R_L = 10k\Omega$



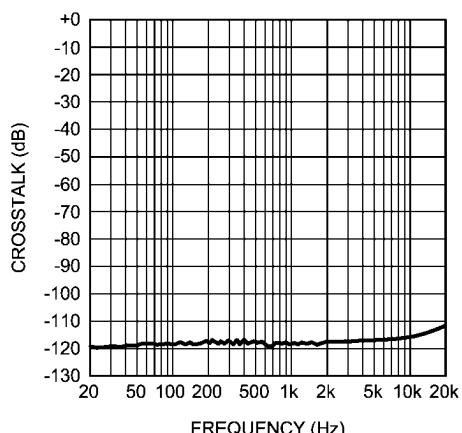
Voltage Noise Density vs Frequency

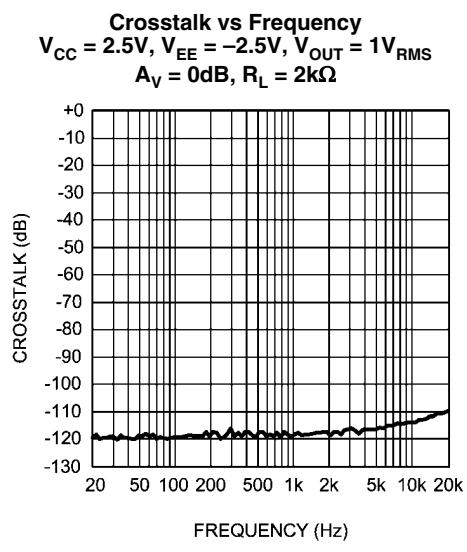
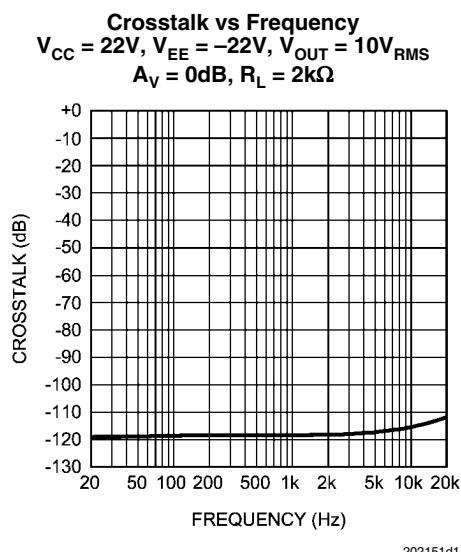
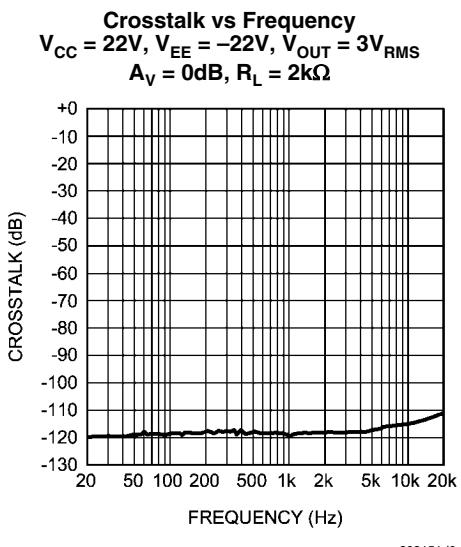
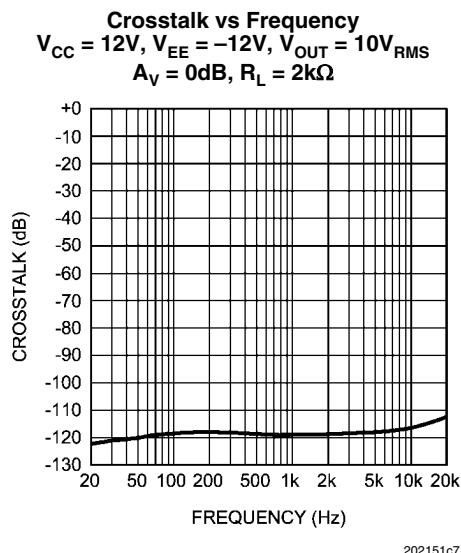
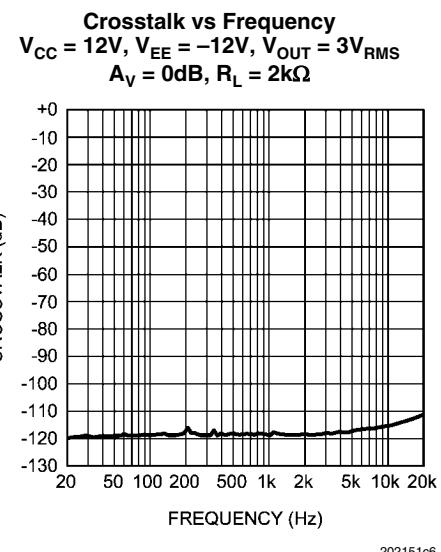
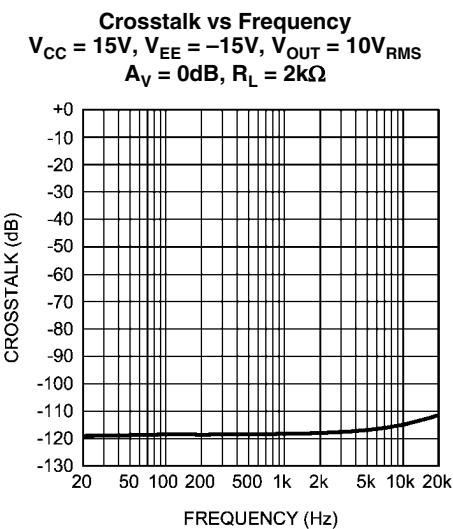


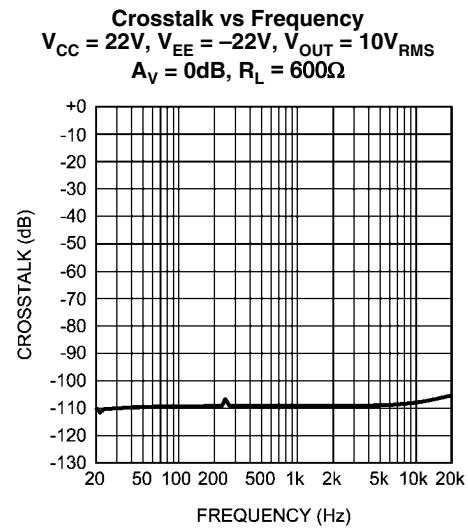
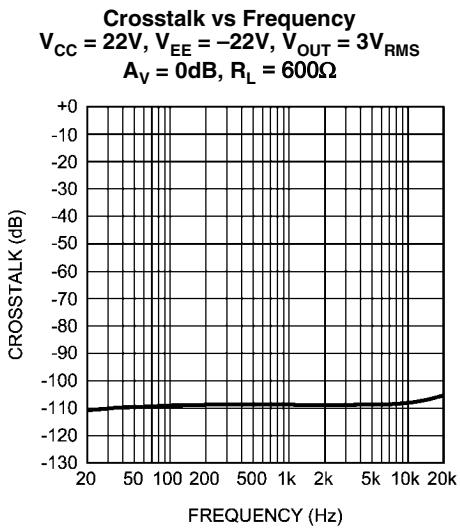
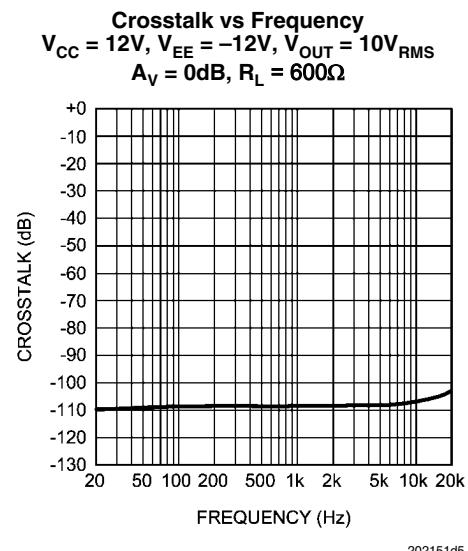
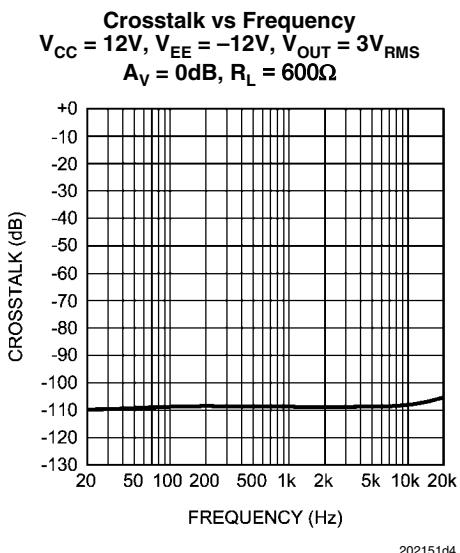
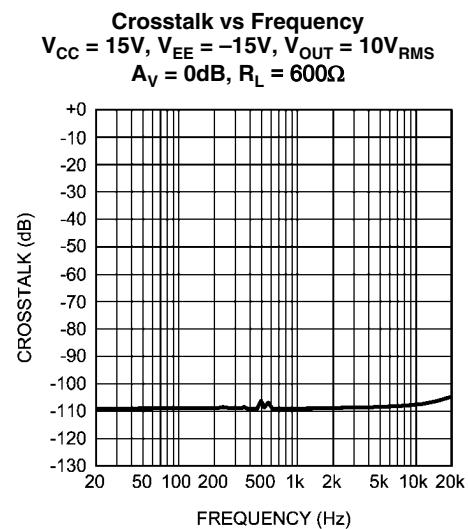
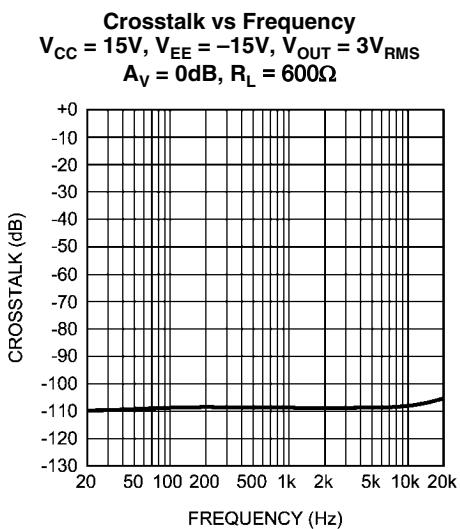
Current Noise Density vs Frequency

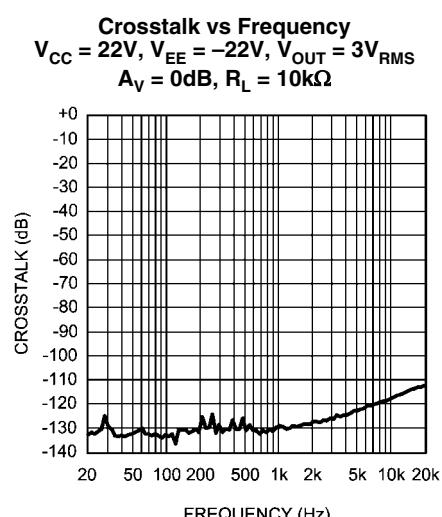
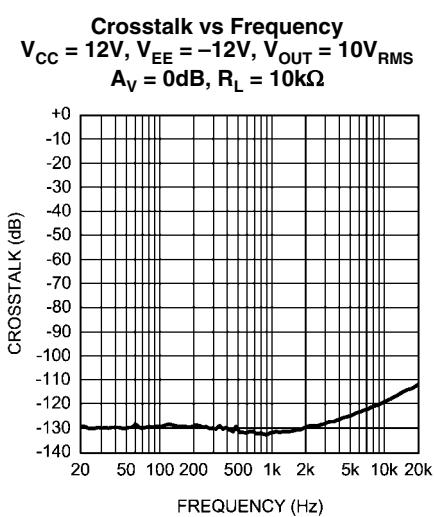
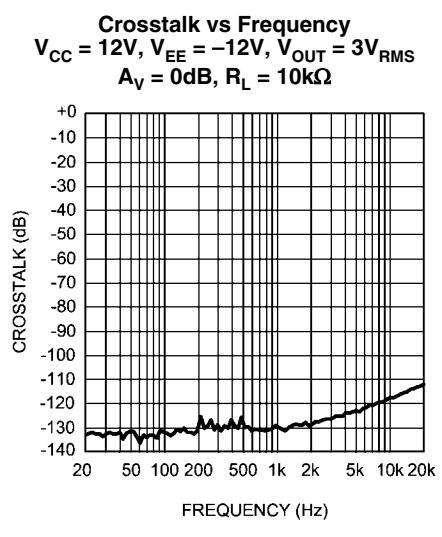
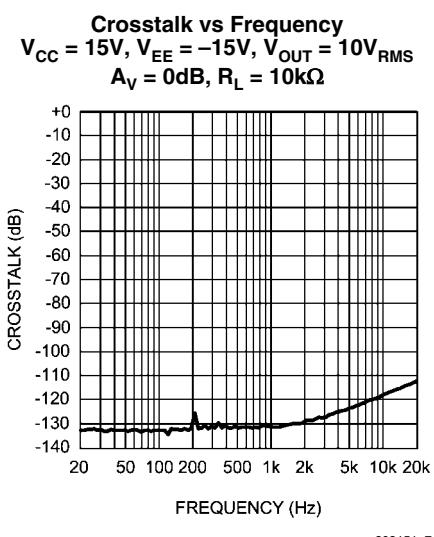
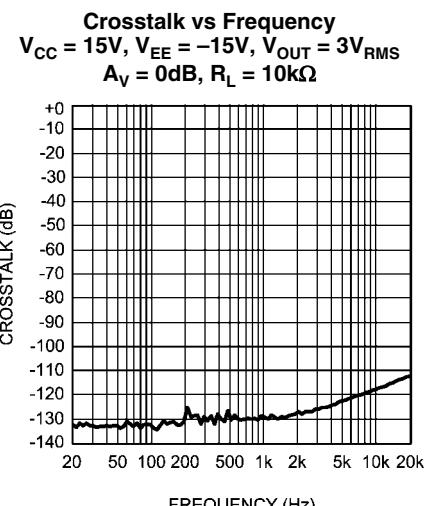
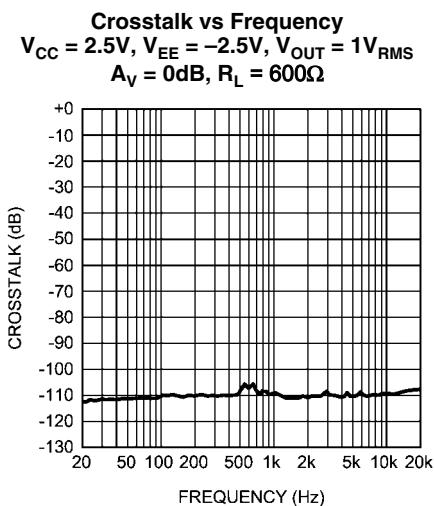


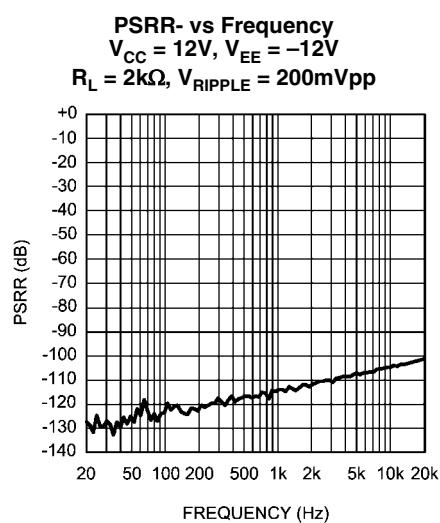
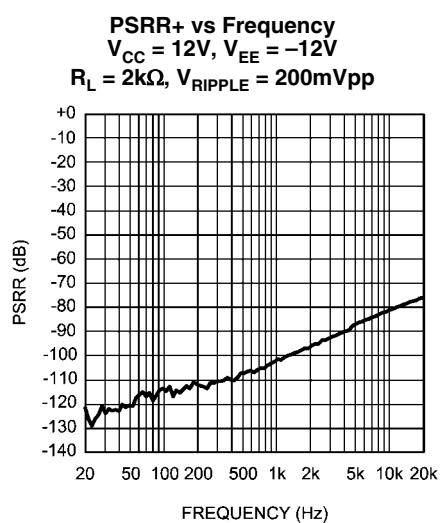
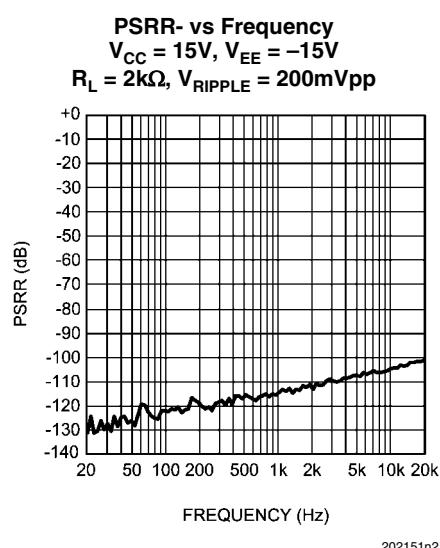
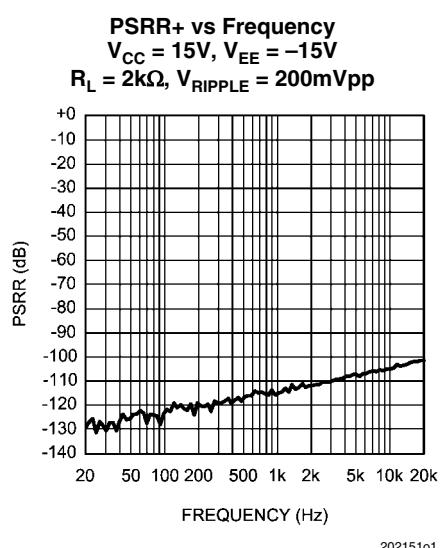
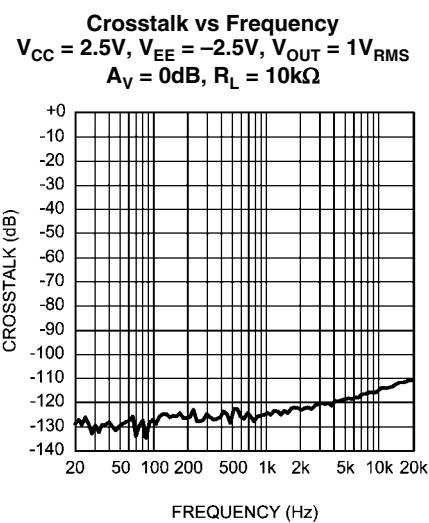
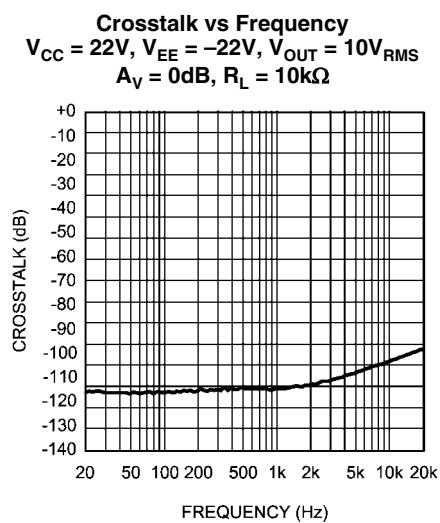
Crosstalk vs Frequency
 $V_{CC} = 15V$, $V_{EE} = -15V$, $V_{OUT} = 3V_{RMS}$
 $A_V = 0dB$, $R_L = 2k\Omega$

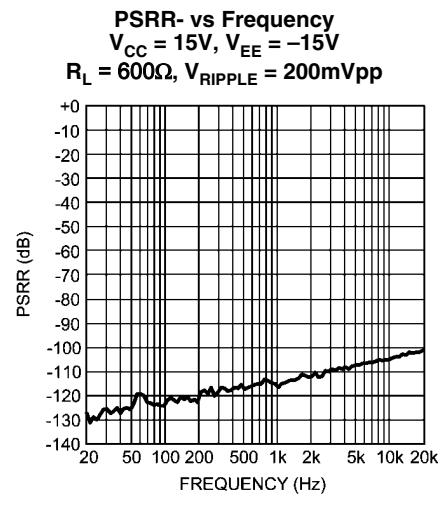
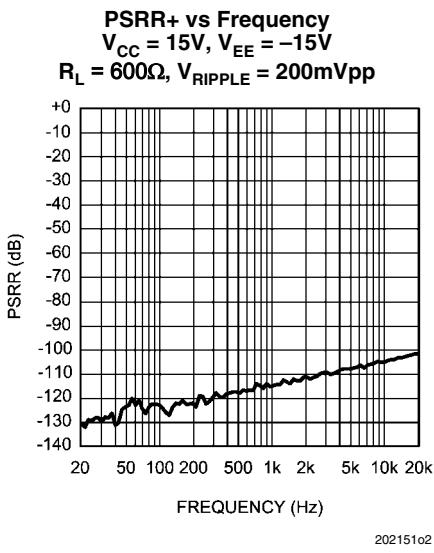
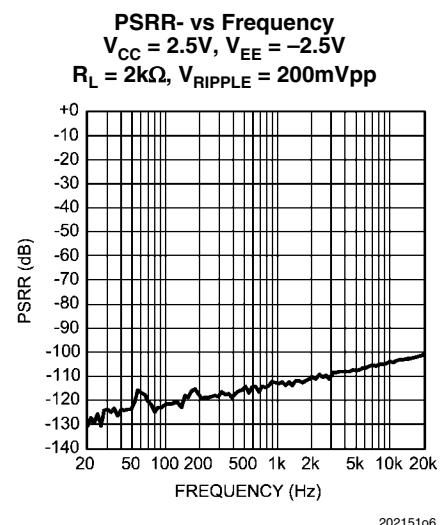
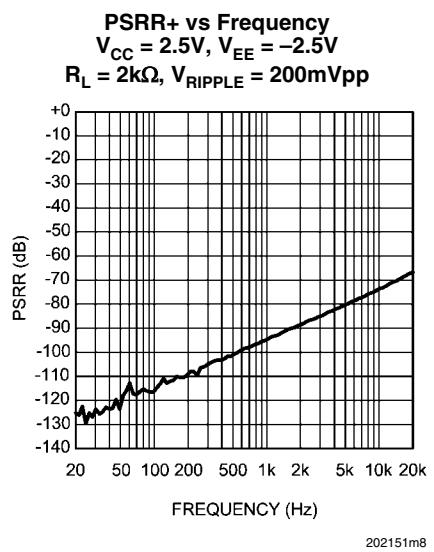
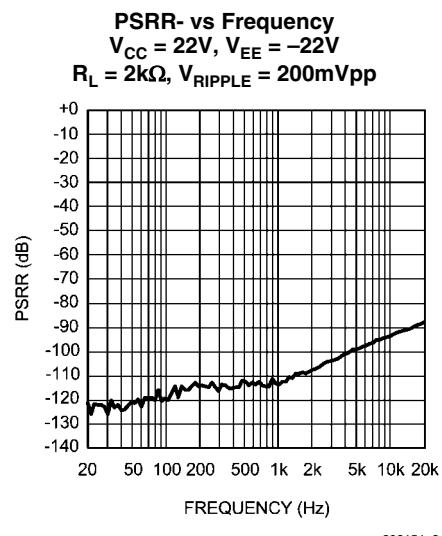
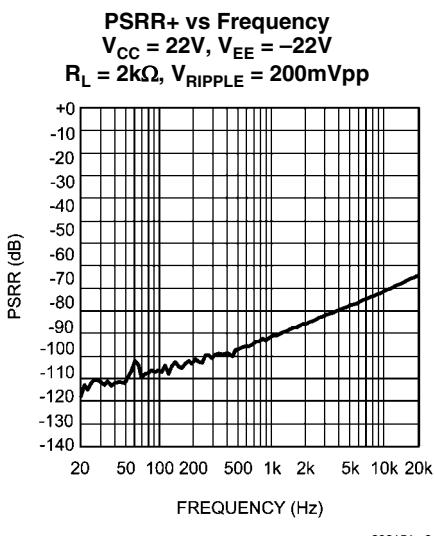


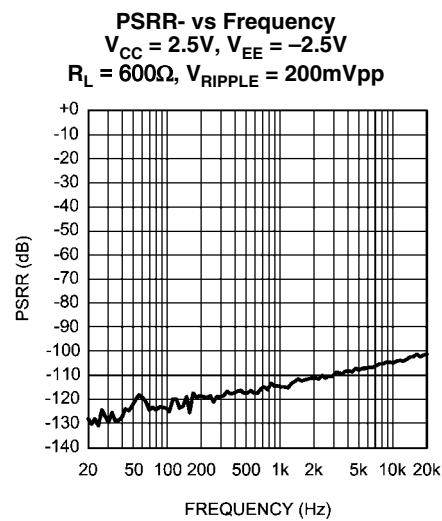
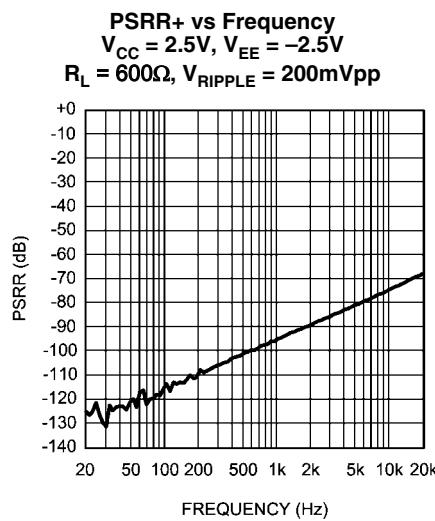
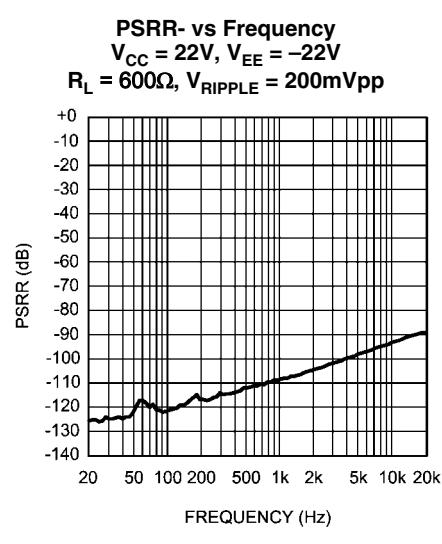
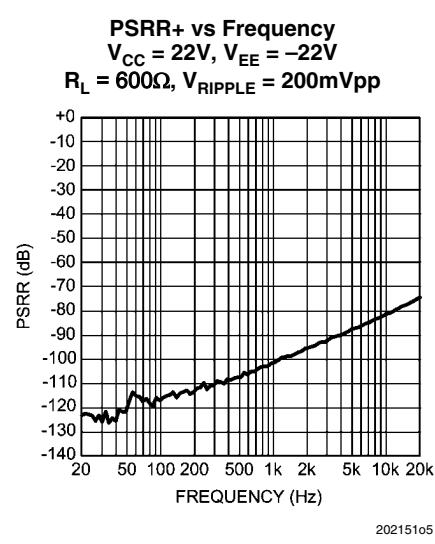
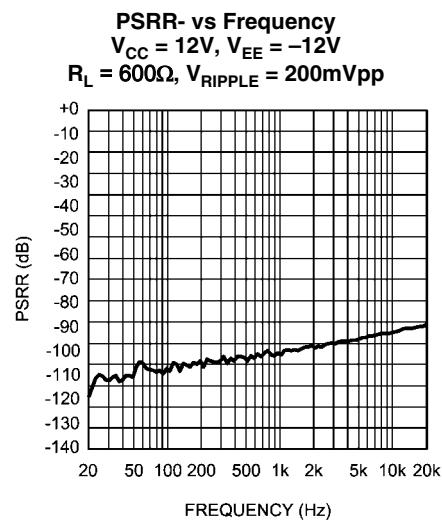
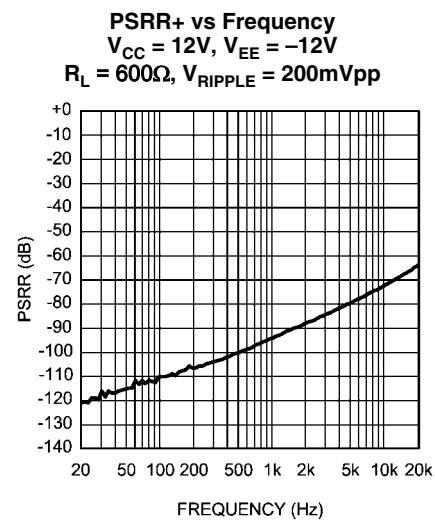


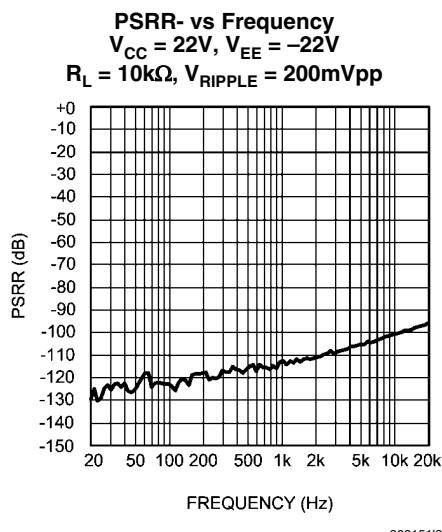
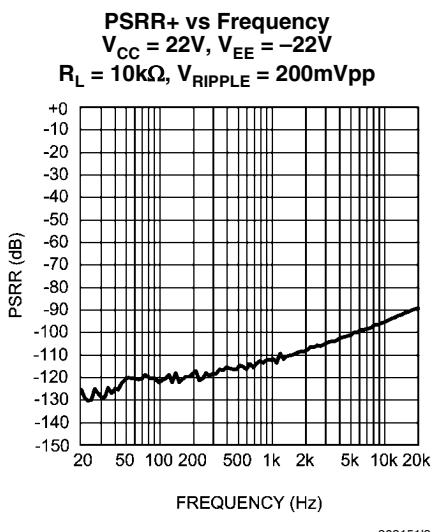
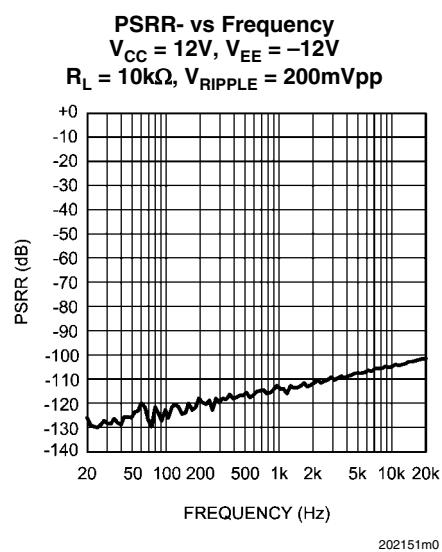
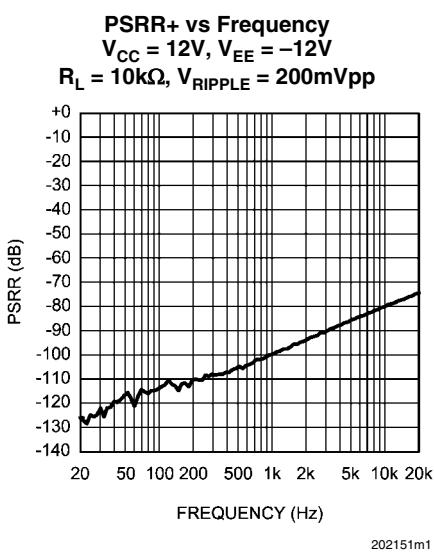
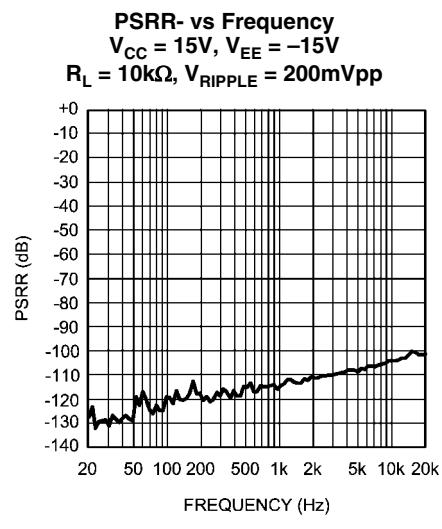
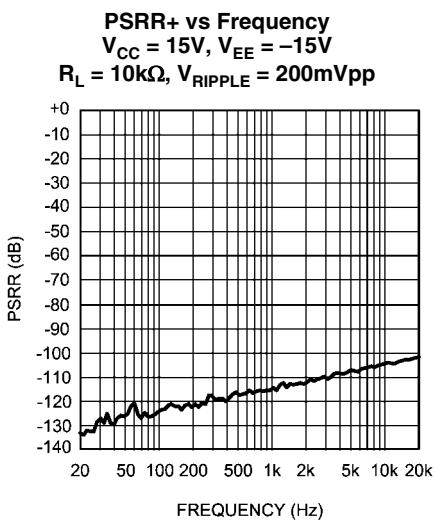


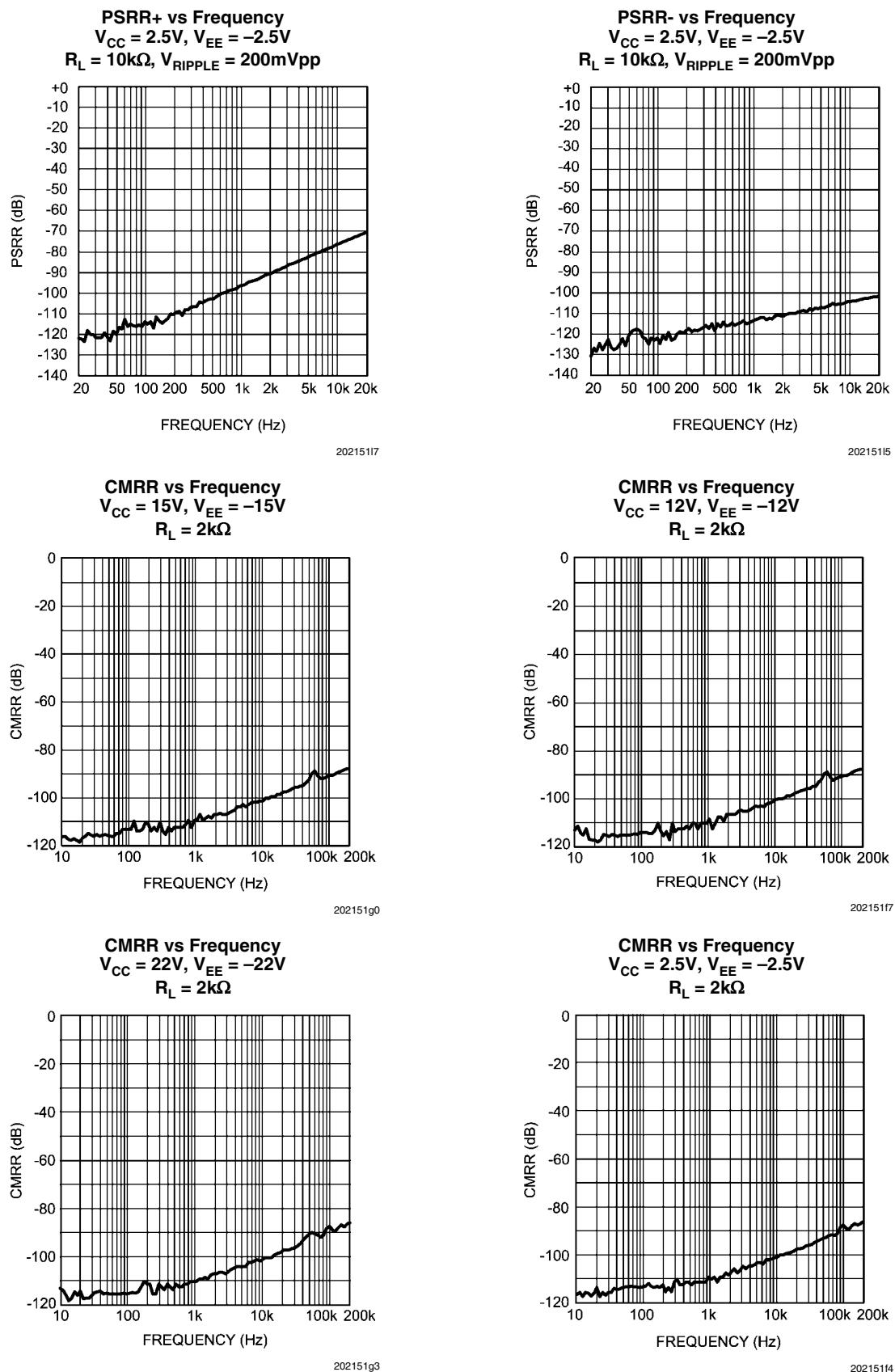


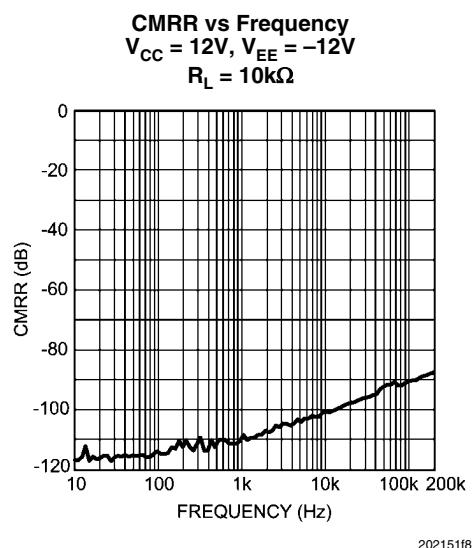
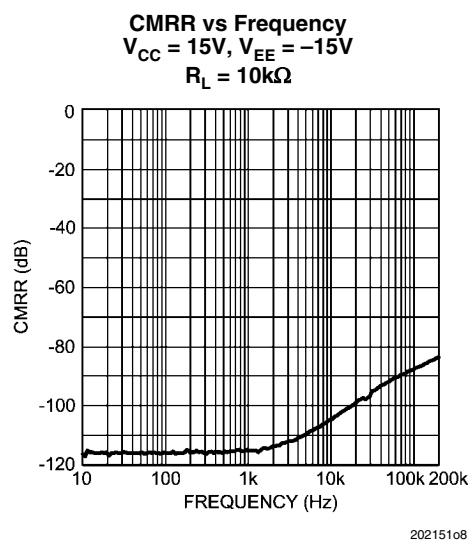
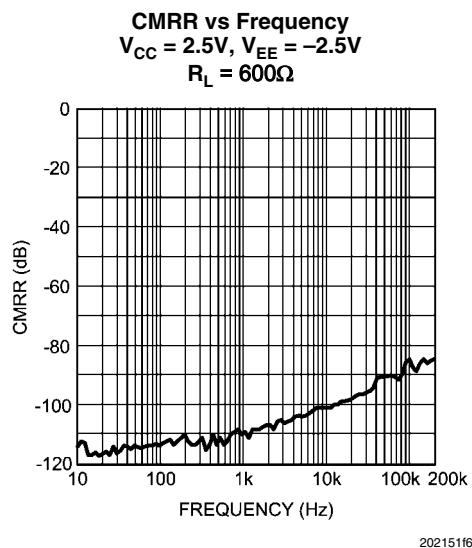
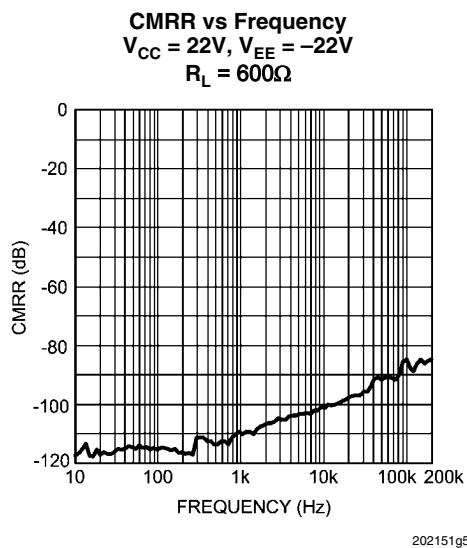
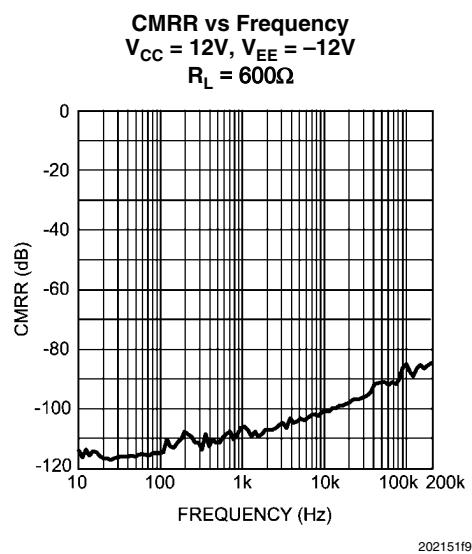
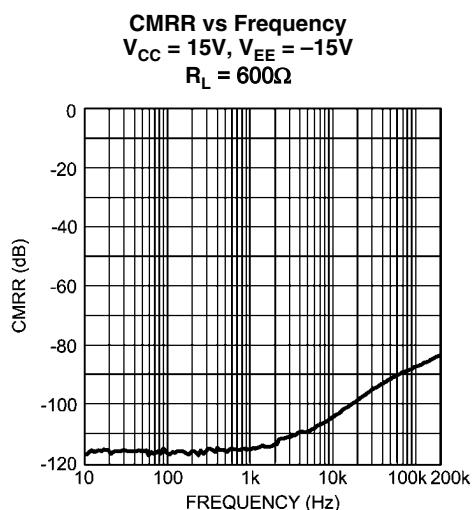


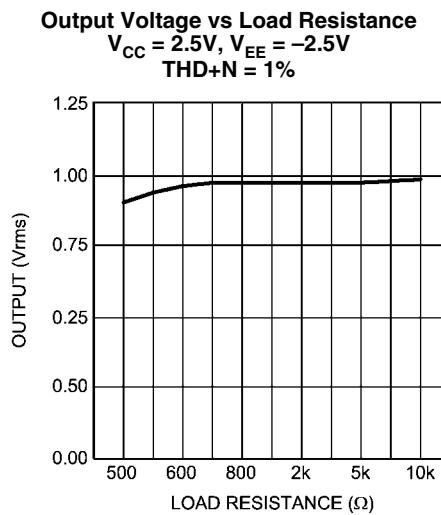
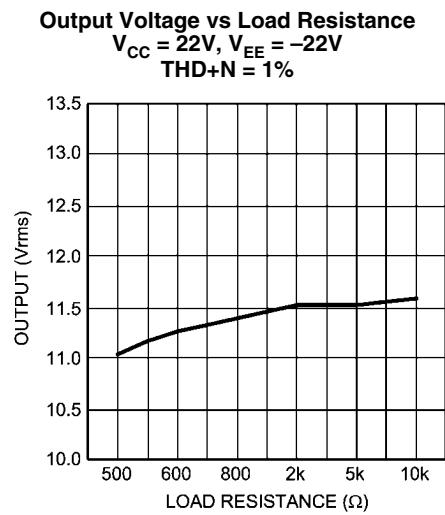
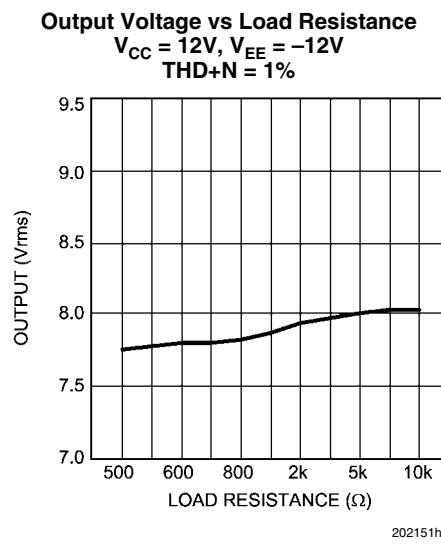
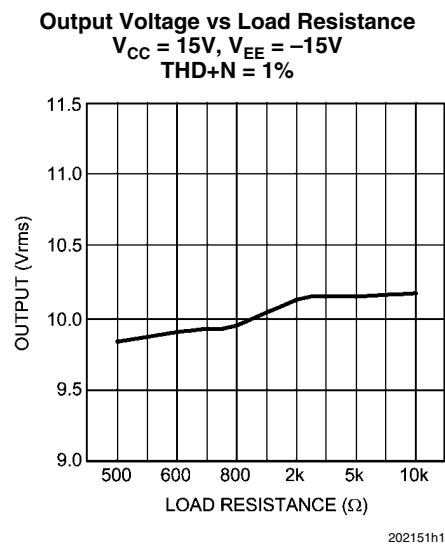
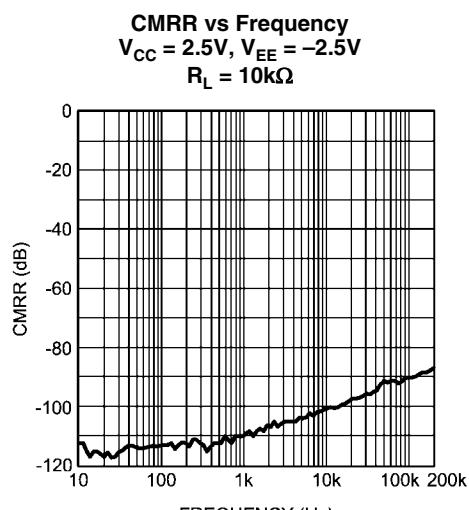
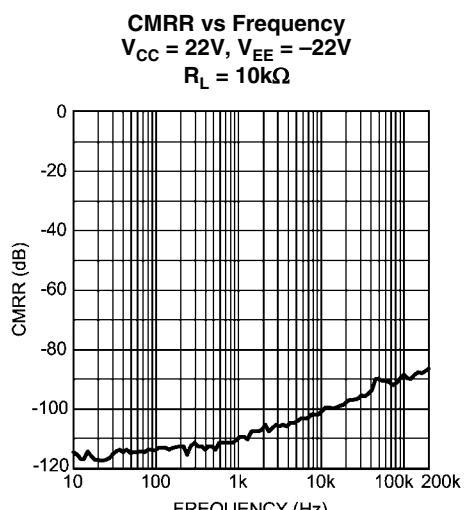




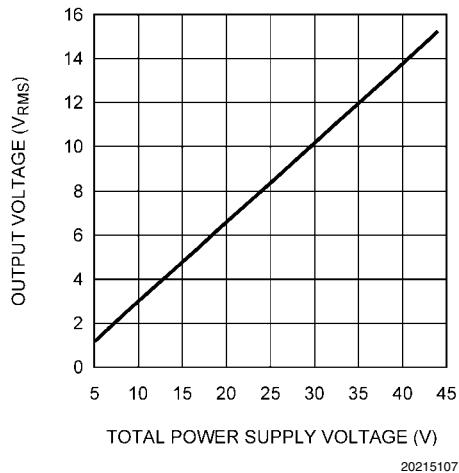




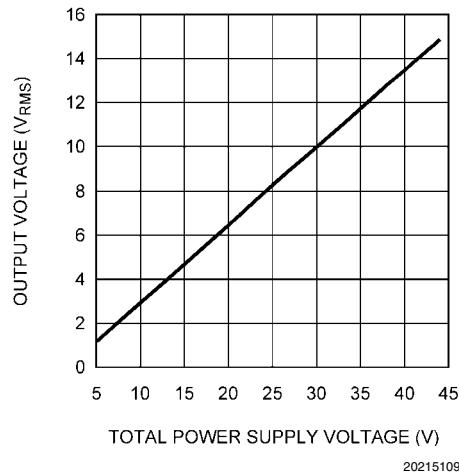




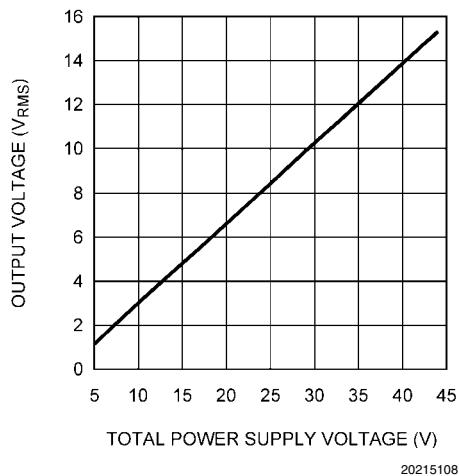
Output Voltage vs Total Power Supply Voltage
 $R_L = 2\text{k}\Omega$, THD+N = 1%



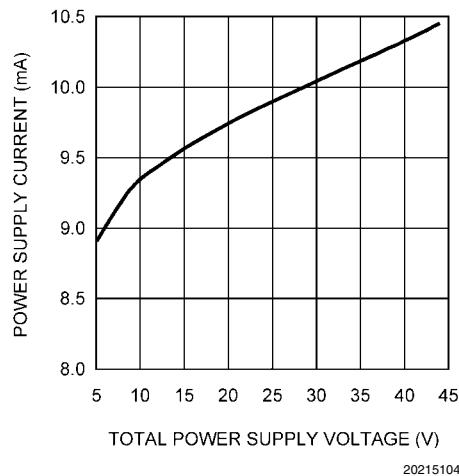
Output Voltage vs Total Power Supply Voltage
 $R_L = 600\Omega$, THD+N = 1%



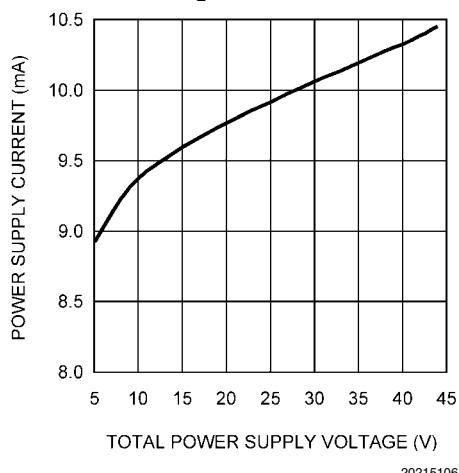
Output Voltage vs Total Power Supply Voltage
 $R_L = 10\text{k}\Omega$, THD+N = 1%



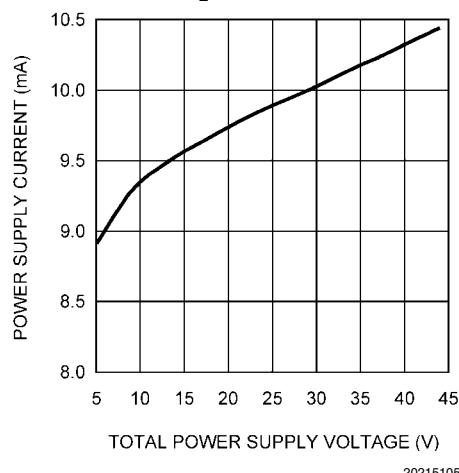
Power Supply Current vs Total Power Supply Voltage
 $R_L = 2\text{k}\Omega$

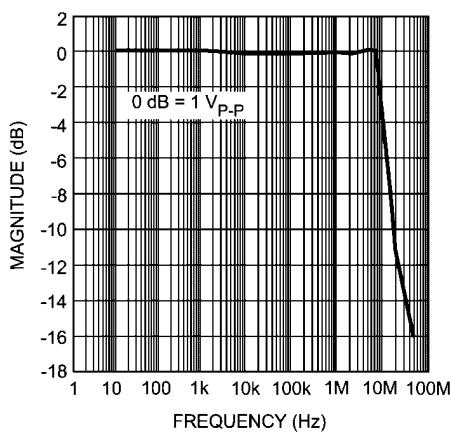


Power Supply Current vs Total Power Supply Voltage
 $R_L = 600\Omega$

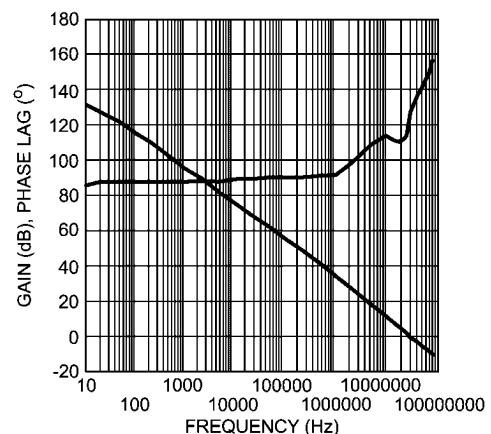


Power Supply Current vs Total Power Supply Voltage
 $R_L = 10\text{k}\Omega$

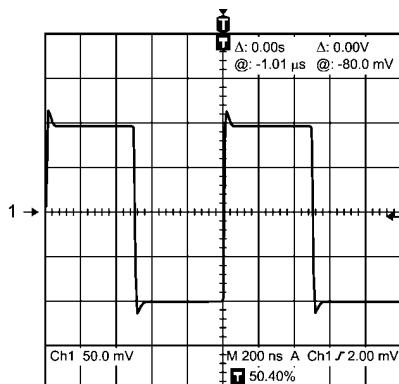


Full Power Bandwidth vs Frequency

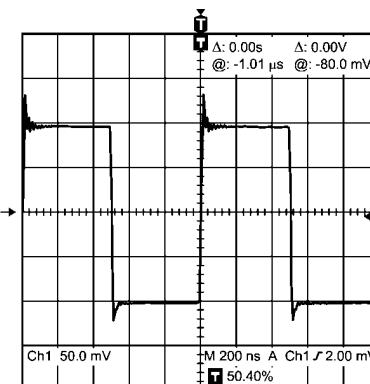
202151j0

Gain Phase vs Frequency

202151j1

Small-Signal Transient Response $A_V = 1, C_L = 10\text{pF}$ 

202151i7

Small-Signal Transient Response $A_V = 1, C_L = 100\text{pF}$ 

202151i8

Application Information

DISTORTION MEASUREMENTS

The vanishingly low residual distortion produced by LME49860 is below the capabilities of all commercially available equipment. This makes distortion measurements just slightly more difficult than simply connecting a distortion meter to the amplifier's inputs and outputs. The solution, however, is quite simple: an additional resistor. Adding this resistor extends the resolution of the distortion measurement equipment.

The LME49860's low residual distortion is an input referred internal error. As shown in Figure 1, adding the 10Ω resistor connected between the amplifier's inverting and non-inverting

inputs changes the amplifier's noise gain. The result is that the error signal (distortion) is amplified by a factor of 101. Although the amplifier's closed-loop gain is unaltered, the feedback available to correct distortion errors is reduced by 101, which means that measurement resolution increases by 101. To ensure minimum effects on distortion measurements, keep the value of R1 low as shown in Figure 1.

This technique is verified by duplicating the measurements with high closed loop gain and/or making the measurements at high frequencies. Doing so produces distortion components that are within the measurement equipment's capabilities. This datasheet's THD+N and IMD values were generated using the above described circuit connected to an Audio Precision System Two Cascade.

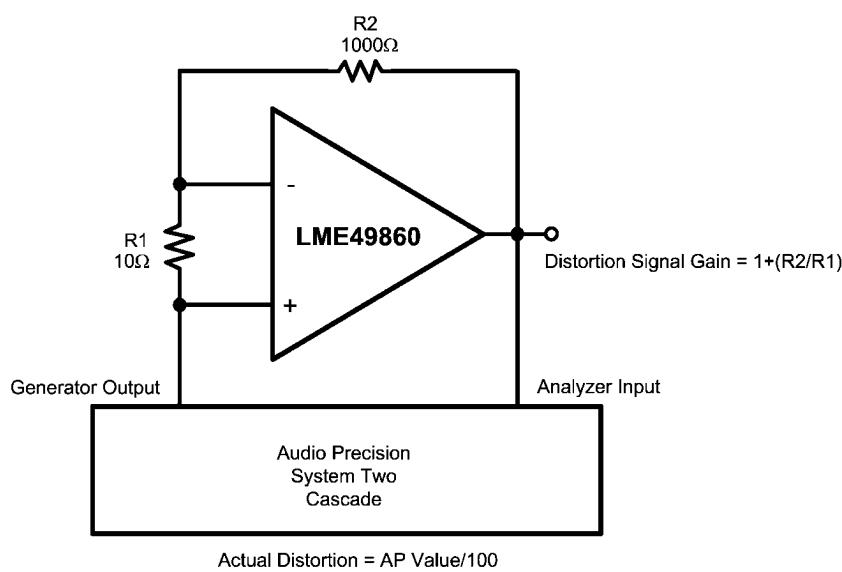
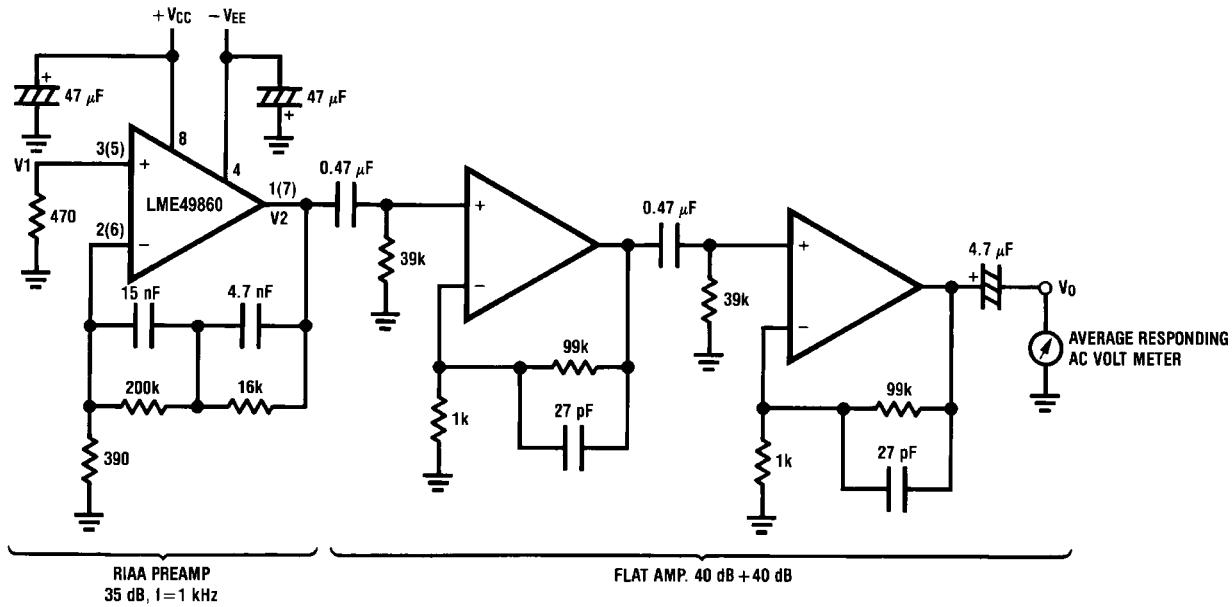


FIGURE 1. THD+N and IMD Distortion Test Circuit

The LME49860 is a high speed op amp with excellent phase margin and stability. Capacitive loads up to 100pF will cause little change in the phase characteristics of the amplifiers and are therefore allowable.

Capacitive loads greater than 100pF must be isolated from the output. The most straightforward way to do this is to put

a resistor in series with the output. This resistor will also prevent excess power dissipation if the output is accidentally shorted.

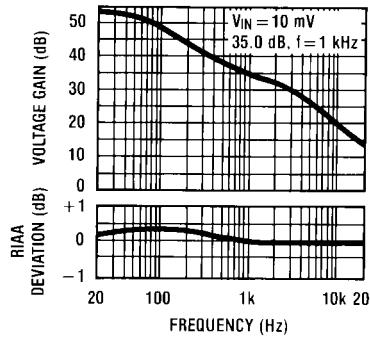


Complete shielding is required to prevent induced pick up from external sources. Always check with oscilloscope for power line noise.

20215127

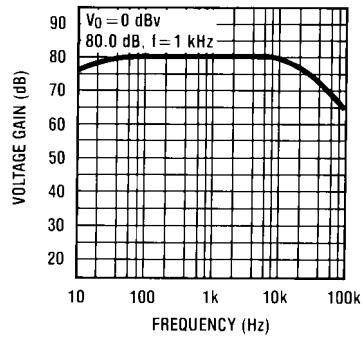
Noise Measurement Circuit
Total Gain: 115 dB @ $f = 1$ kHz
Input Referred Noise Voltage: $e_n = V_0/560,000$ (V)

RIAA Preamplifier Voltage Gain, RIAA Deviation vs Frequency



20215128

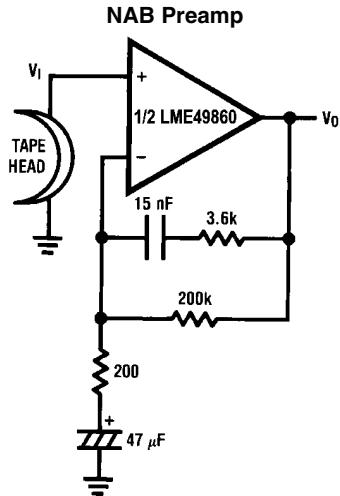
Flat Amp Voltage Gain vs Frequency



20215129

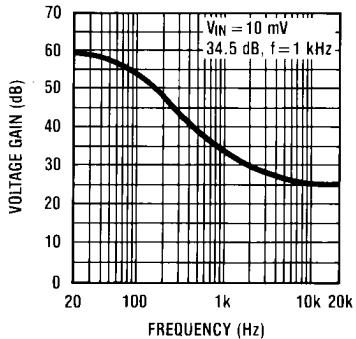


TYPICAL APPLICATIONS

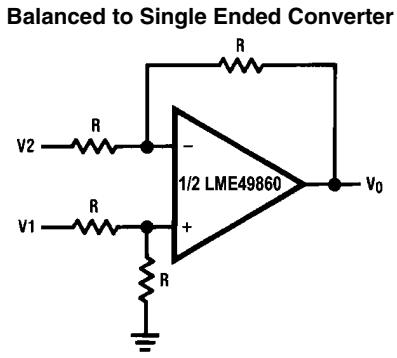


20215130

$A_V = 34.5$
 $F = 1 \text{ kHz}$
 $E_n = 0.38 \mu\text{V}$
A Weighted

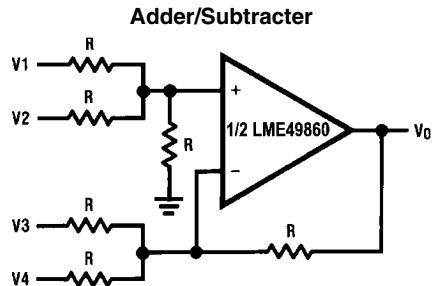
NAB Preamp Voltage Gain vs Frequency

20215131



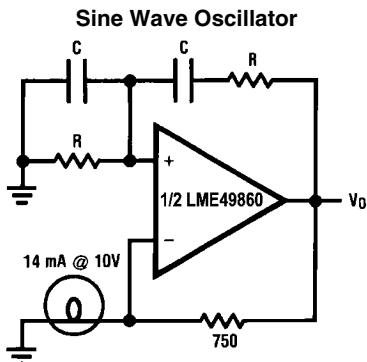
20215132

$V_O = V_1 - V_2$



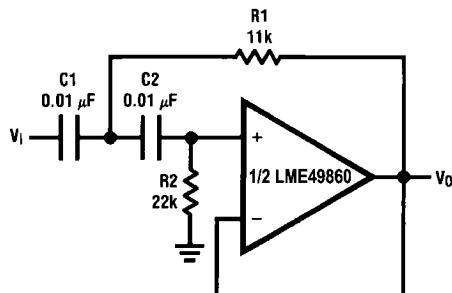
20215133

$$V_O = V_1 + V_2 - V_3 - V_4$$

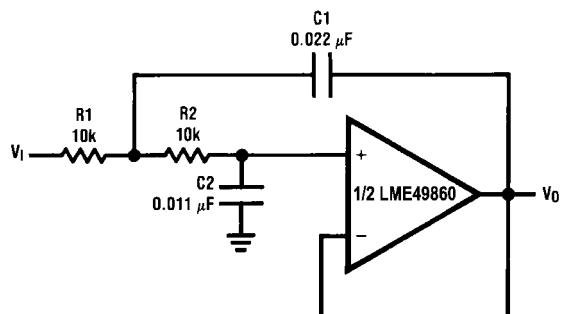


20215134

$$f_o = \frac{1}{2\pi RC}$$

**Second Order High Pass Filter
(Butterworth)**


20215135

**Second Order Low Pass Filter
(Butterworth)**


20215136

if $C_1 = C_2 = C$

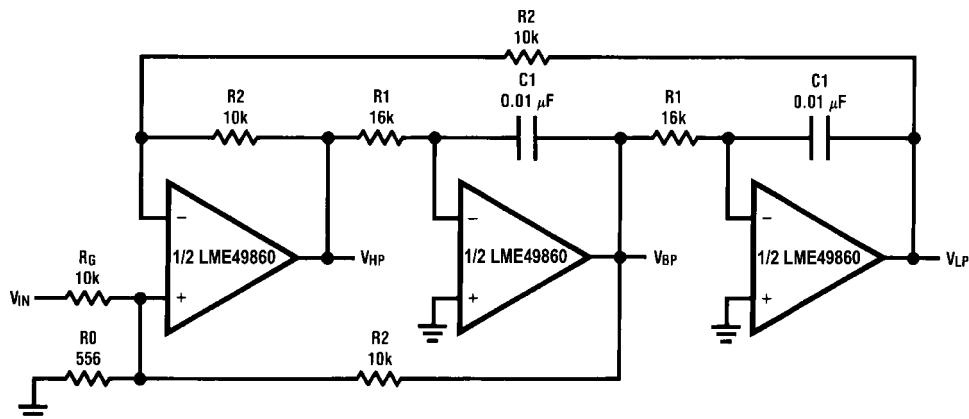
$$R_1 = \frac{\sqrt{2}}{2\omega_0 C}$$

$$R_2 = 2 \cdot R_1$$

Illustration is $f_0 = 1$ kHzif $R_1 = R_2 = R$

$$C_1 = \frac{\sqrt{2}}{\omega_0 R}$$

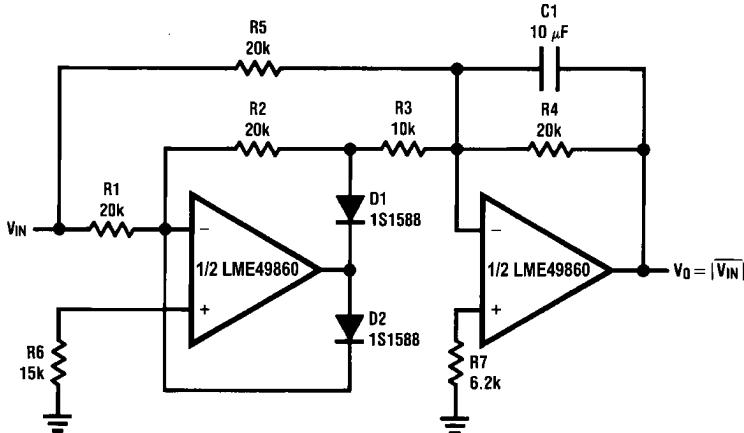
$$C_2 = \frac{C_1}{2}$$

Illustration is $f_0 = 1$ kHz
State Variable Filter


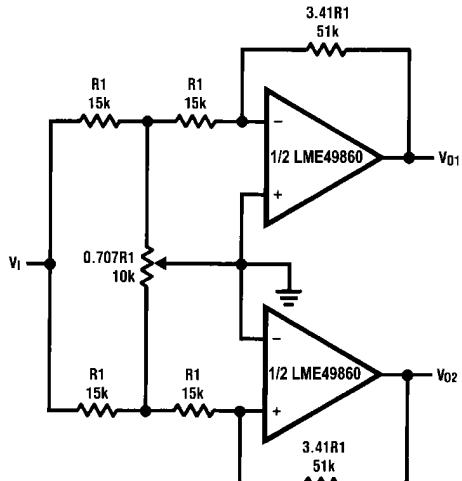
20215137

$$f_0 = \frac{1}{2\pi C_1 R_1}, Q = \frac{1}{2} \left(1 + \frac{R_2}{R_0} + \frac{R_2}{R_G} \right), A_{BP} = QA_{LP} = QA_{LH} = \frac{R_2}{R_G}$$

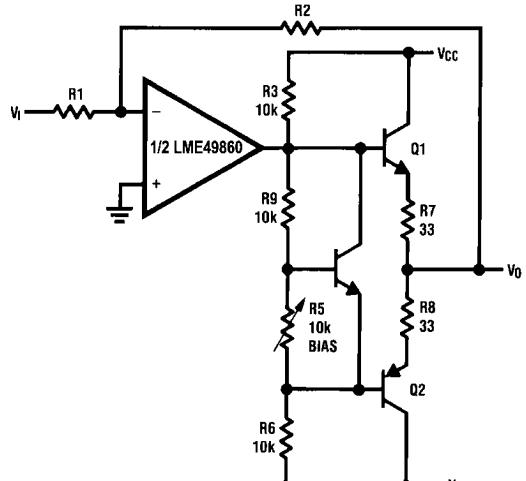
Illustration is $f_0 = 1$ kHz, $Q = 10$, $A_{BP} = 1$

AC/DC Converter

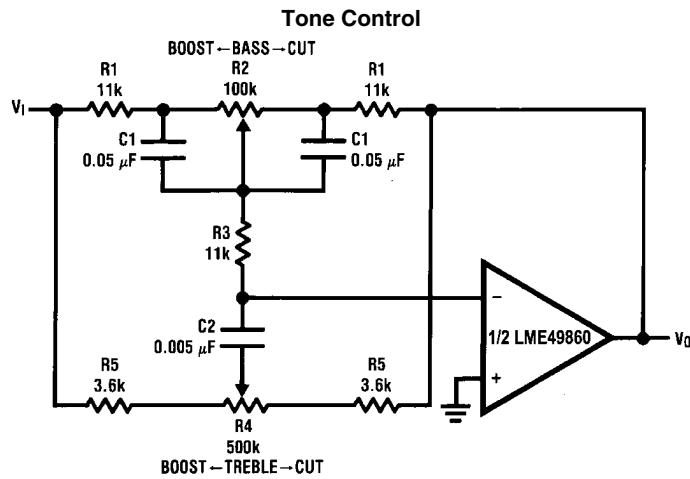
20215138

2 Channel Panning Circuit (Pan Pot)

20215139

Line Driver

20215140

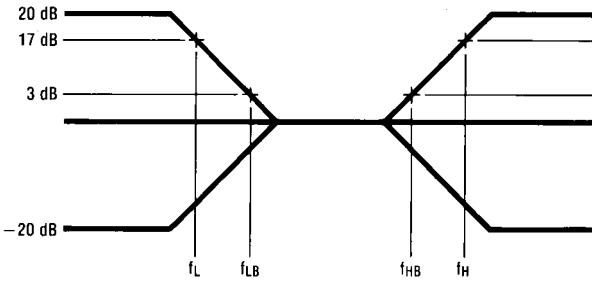


20215141

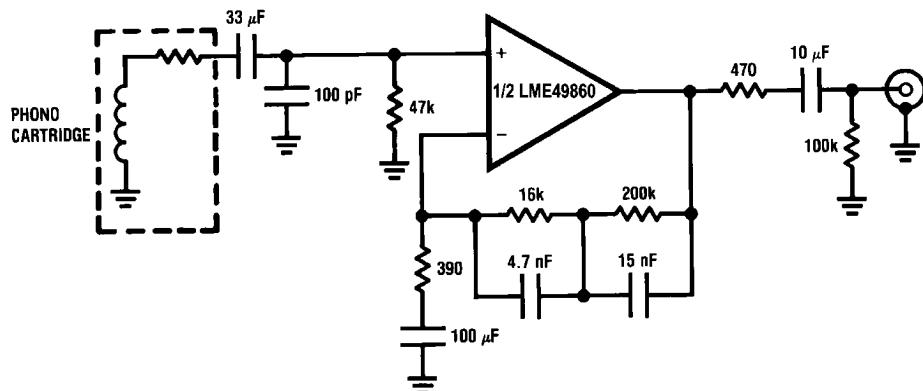
$$f_L = \frac{1}{2\pi R_2 C_1}, f_{LB} = \frac{1}{2\pi R_1 C_1}$$

$$f_H = \frac{1}{2\pi R_5 C_2}, f_{HB} = \frac{1}{2\pi(R_1 + R_5 + 2R_3)C_2}$$

Illustration is:

 $f_L = 32$ Hz, $f_{LB} = 320$ Hz $f_H = 11$ kHz, $f_{HB} = 1.1$ kHz

20215142

RIAA Preamp

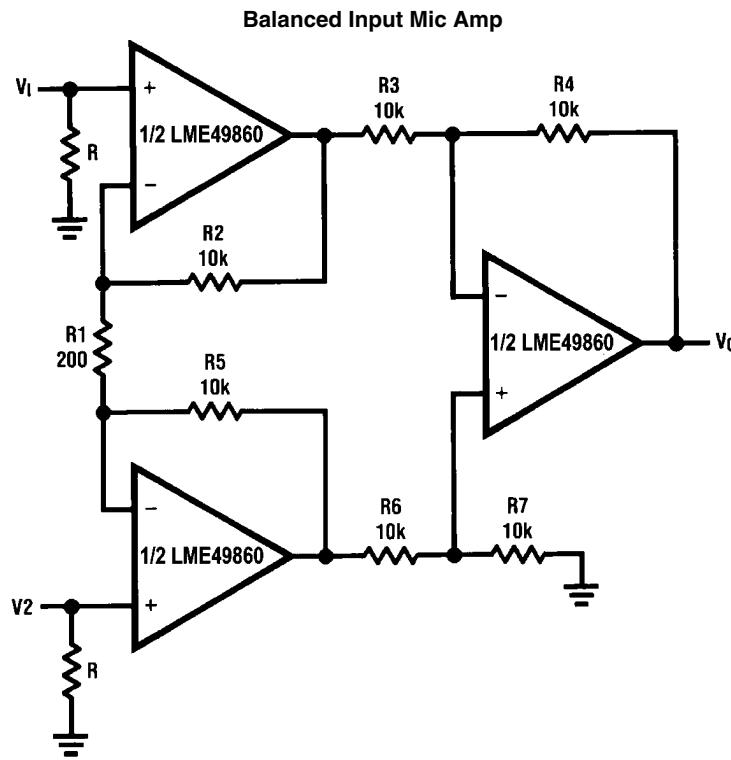
20215103

 $A_v = 35$ dB $E_n = 0.33$ μV $S/N = 90$ dB $f = 1$ kHz

A Weighted

A Weighted, $V_{IN} = 10$ mV

@f = 1 kHz



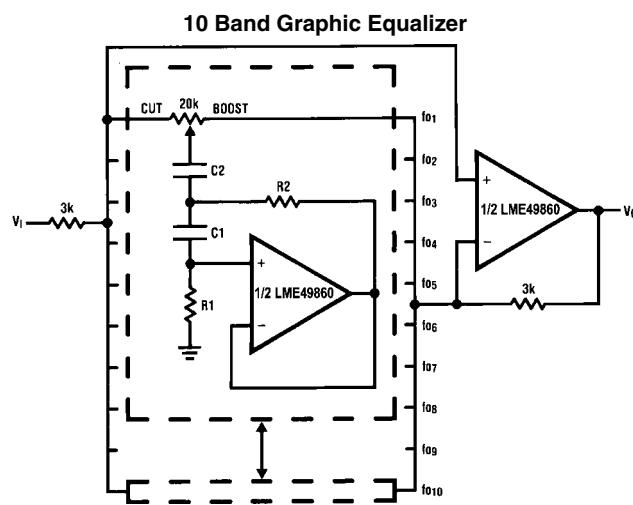
20215143

If R₂ = R₅, R₃ = R₆, R₄ = R₇

$$V_0 = \left(1 + \frac{2R_2}{R_1}\right) \frac{R_4}{R_3} (V_2 - V_1)$$

Illustration is:

$$V_0 = 10(V_2 - V_1)$$



20215144

f₀ (Hz)	C₁	C₂	R₁	R₂
32	0.12µF	4.7µF	75kΩ	500Ω
64	0.056µF	3.3µF	68kΩ	510Ω
125	0.033µF	1.5µF	62kΩ	510Ω
250	0.015µF	0.82µF	68kΩ	470Ω
500	8200pF	0.39µF	62kΩ	470Ω
1k	3900pF	0.22µF	68kΩ	470Ω
2k	2000pF	0.1µF	68kΩ	470Ω
4k	1100pF	0.056µF	62kΩ	470Ω
8k	510pF	0.022µF	68kΩ	510Ω
16k	330pF	0.012µF	51kΩ	510Ω

Note 9: At volume of change = ±12 dB

Q = 1.7

Reference: "AUDIO/RADIO HANDBOOK", National Semiconductor, 1980, Page 2-61

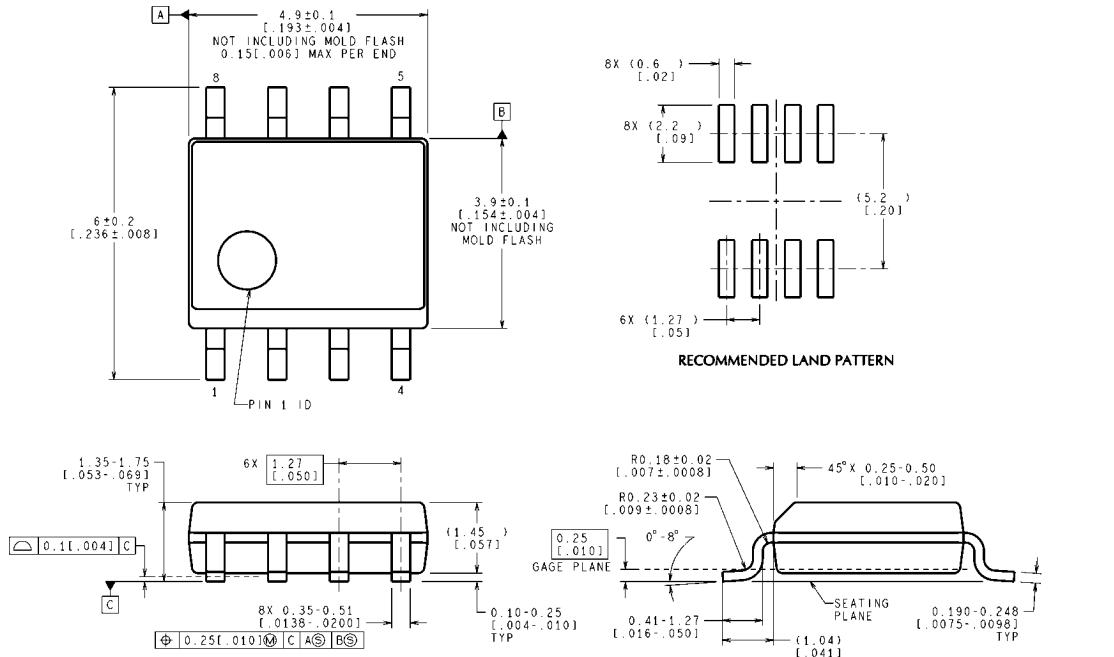


Revision History

Rev	Date	Description
1.0	06/01/07	Initial release.
1.1	06/11/07	Added the LME49860MA and LME49860NA Top Mark Information.



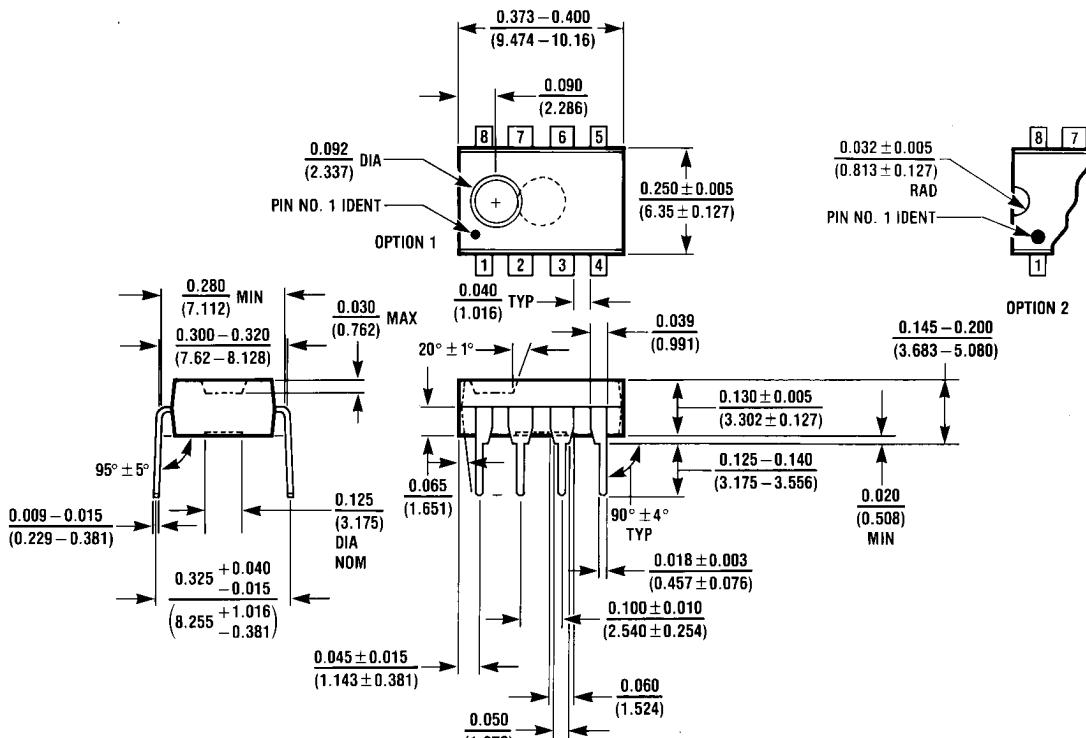
Physical Dimensions inches (millimeters) unless otherwise noted



CONTROLLING DIMENSION IS MILLIMETER
VALUES IN [] ARE INCHES
DIMENSIONS IN () FOR REFERENCE ONLY

M08A (Rev L)

Narrow SOIC Package
Order Number LME49860MA
NS Package Number M08A



Dual-In-Line Package
Order Number LME49860NA
NS Package Number N08E

N08E (REV F)



Notes

LME49860



Notes

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Email: europe.support@nsc.com
Deutsch Tel: +49 (0) 69 9508 6208
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**National Semiconductor Asia
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Email: ap.support@nsc.com

**National Semiconductor Japan
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